

University of Stuttgart
Institute for Materials Science

Synthesis methods for complex oxides and intermetallics for high temperature thermoelectric converters

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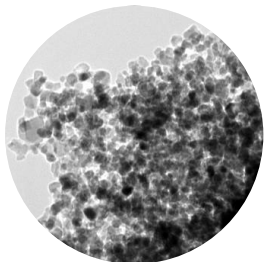
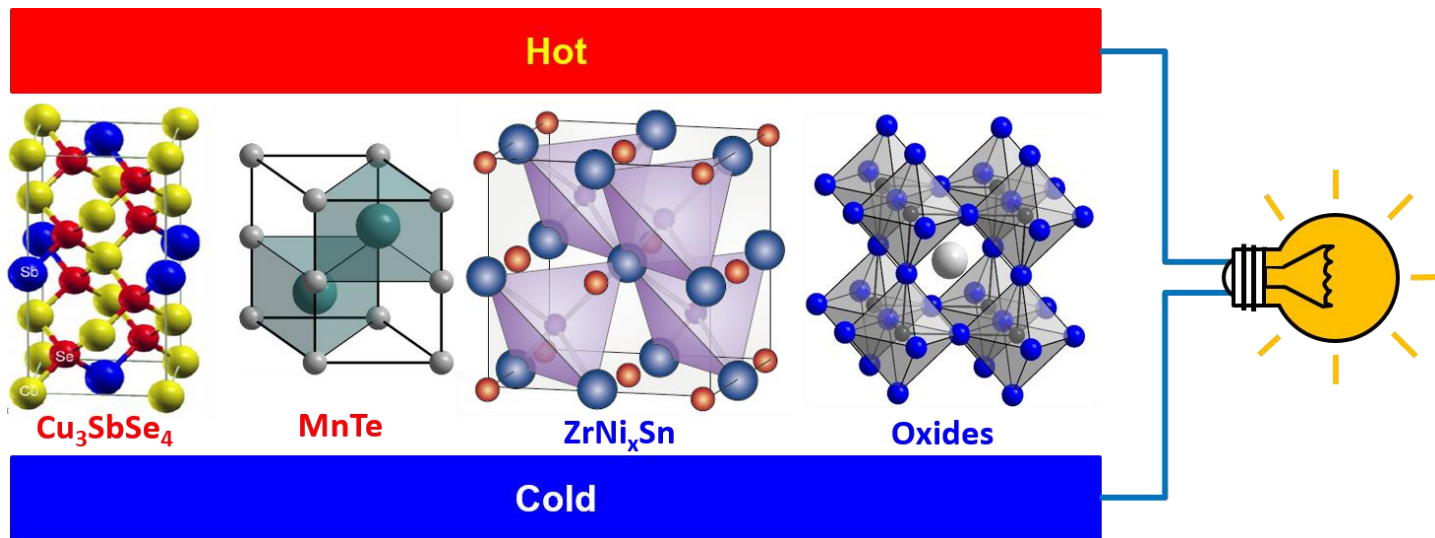


happy



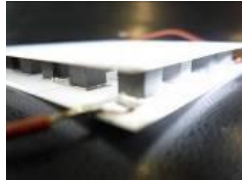
day

Motivation



- Structure property relation
- High Temperature Ceramic Converters
- Soft-chemistry synthesis
- Perovskite-type Titanates
- Half-Heusler Materials

Tailoring of TE materials



>1W/cm²

test

applications

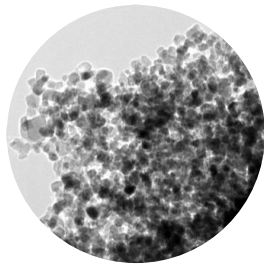
- High thermal heat flow conversion vs. thermal insulation
- transp.prop., regenerativity, ..

characterisation

- DoS, structure, comp.
- Defect structure
- Dynamic behavior

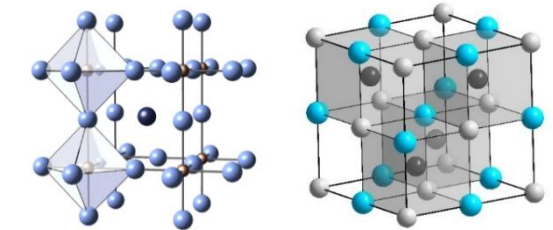
function, form,

scalability



synthesis

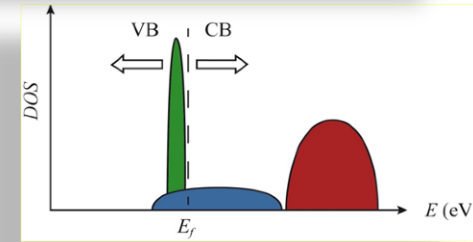
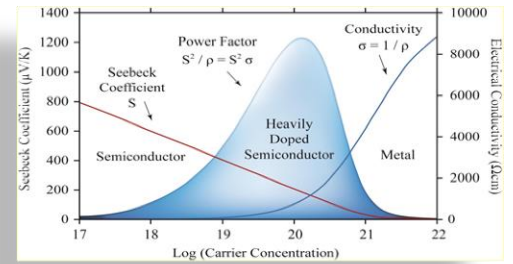
- "chimie douce", USC, flame spray, flux, MW, plasma
- Homogenation, densification
- Single Crystals



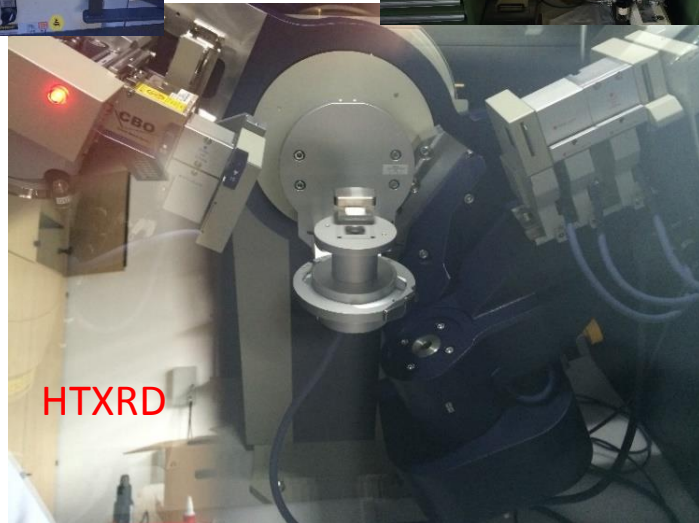
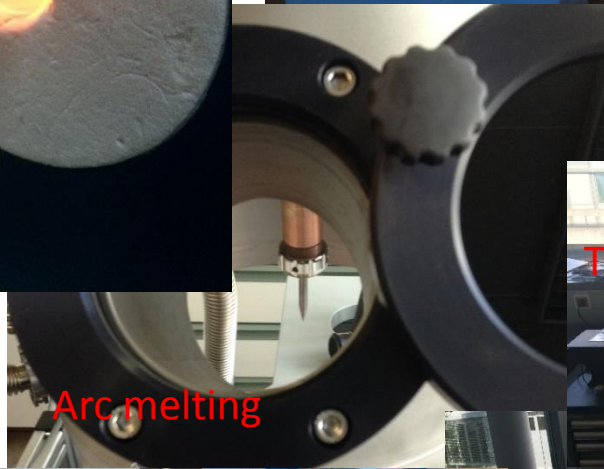
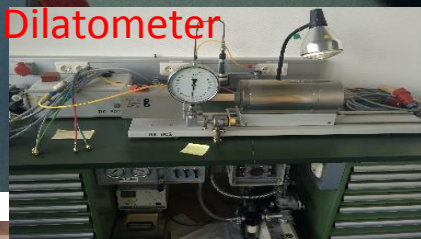
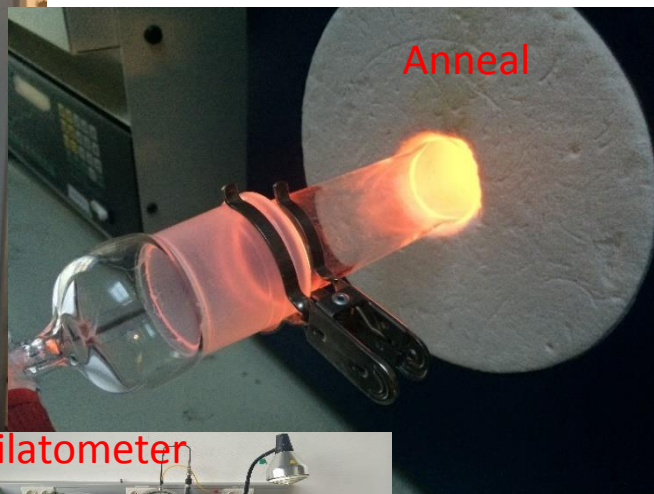
materials choice

- PGEC
- perovskites-type oxides
- heusler compounds

Design rules

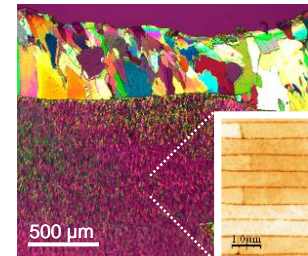
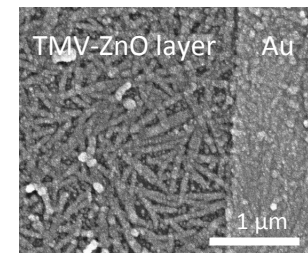
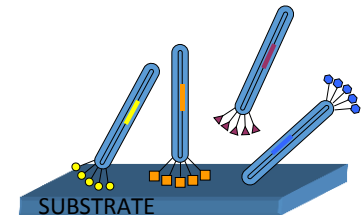
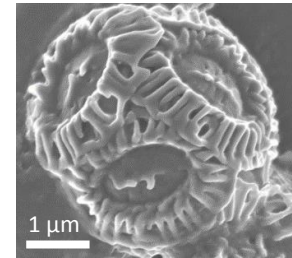


HT Synthesis and Characterisation Equipment

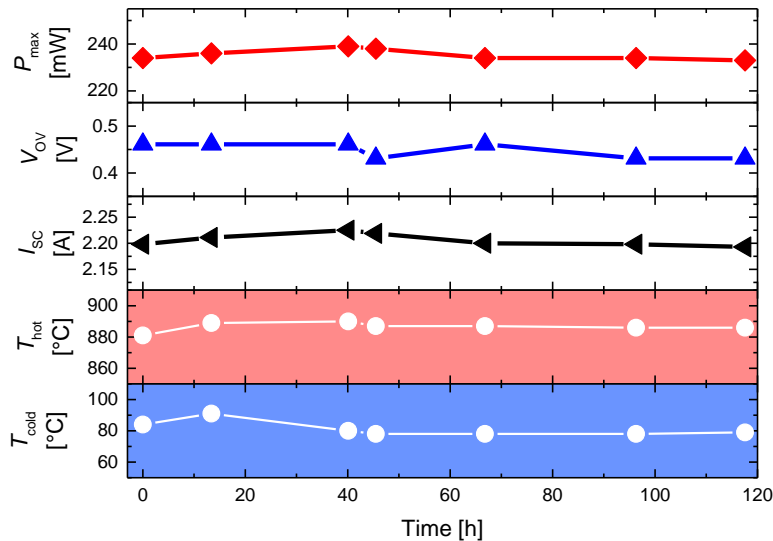
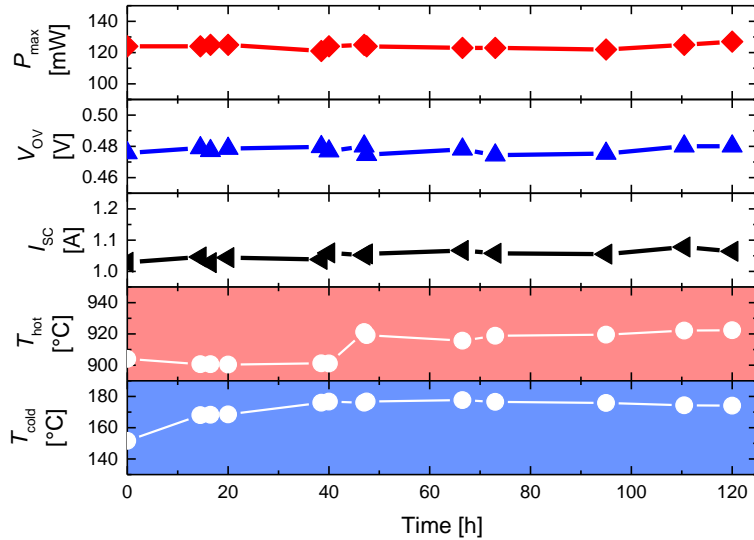


Materials Synthesis Directed by Biological Templates

- Biomineralization of materials with microalgae
- Mineralization using specifically interacting peptides
- Nano-structuring with bio-templates
- Biomineral structures as models for new functions



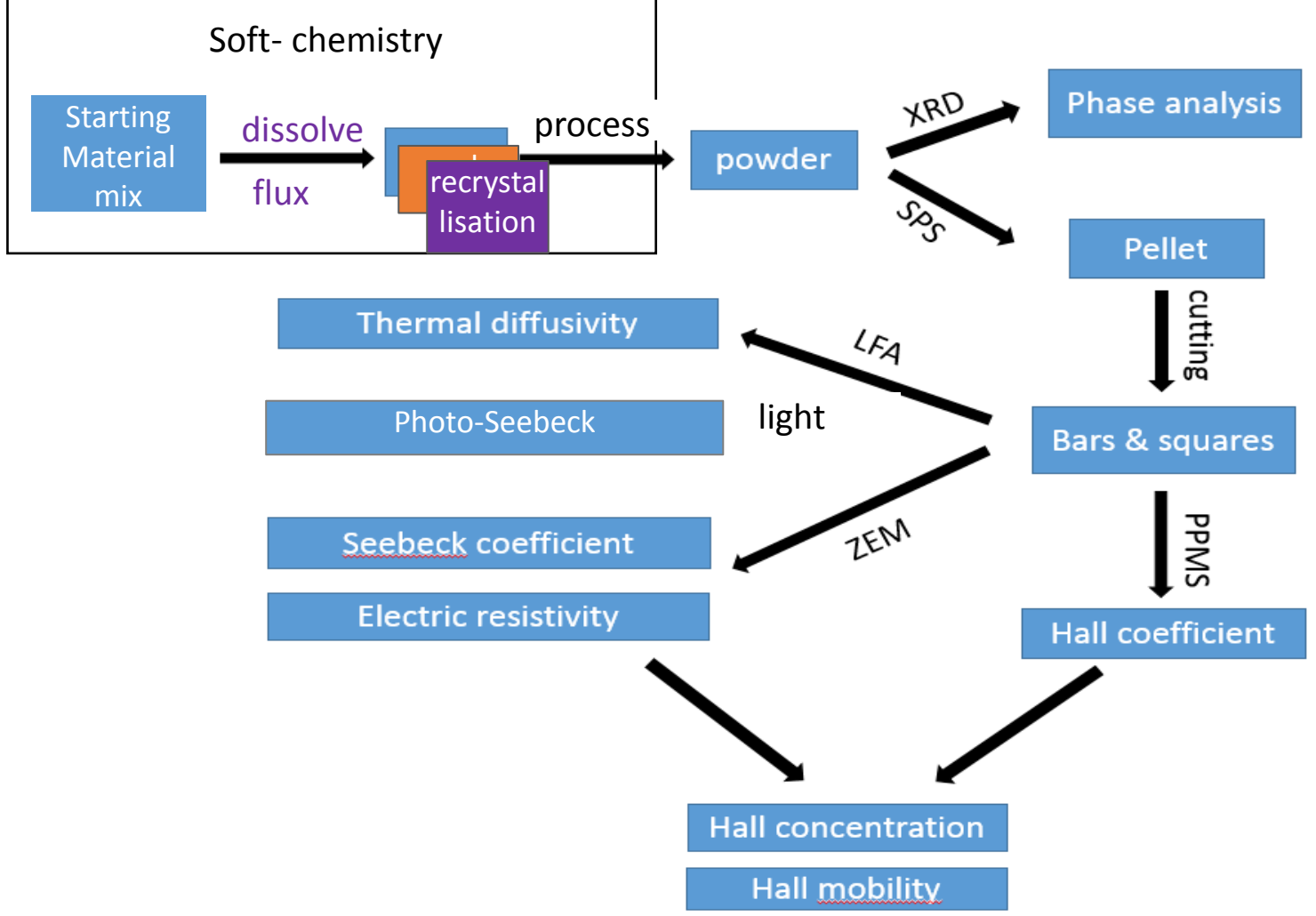
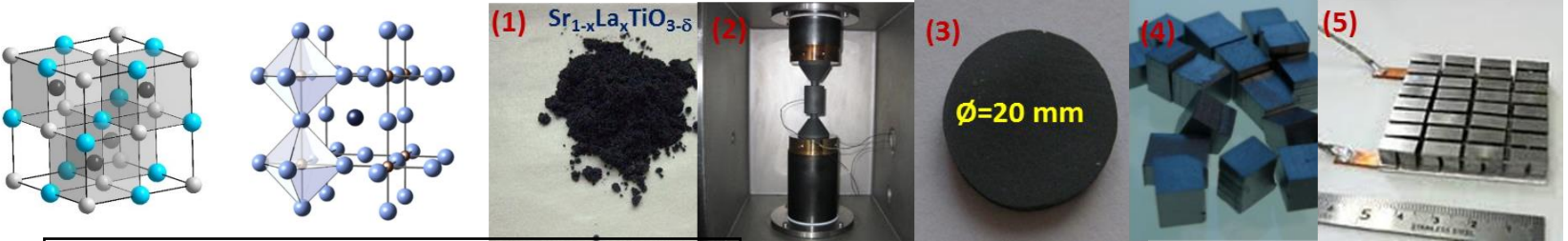
Stability tests (>100h)



- High power density: 1.4 W/cm³
- No degradation during 110 h of high temperature thermoelectric conversion

Saucke, G., Populoh, S., Thiel, P., Xie, W., Funahashi, R. and Weidenkaff, A., Journal of Applied Physics, 118, (2015) 035106.

Experimental



W. Xie, T. Zou

Titanates: EuTiO_3 ceramics

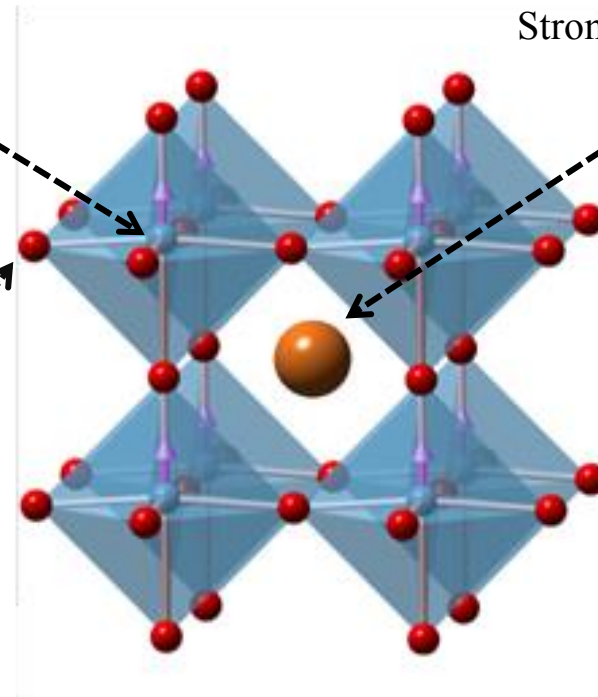
- Perovskite structure ABO_3 ($Pm\bar{3}m$ symmetry)
- Structural distortion below RT [1]



Transition metal
3d electrons
Strongly correlated
electrons

Ti^{4+}

O^{2-}
octahedron



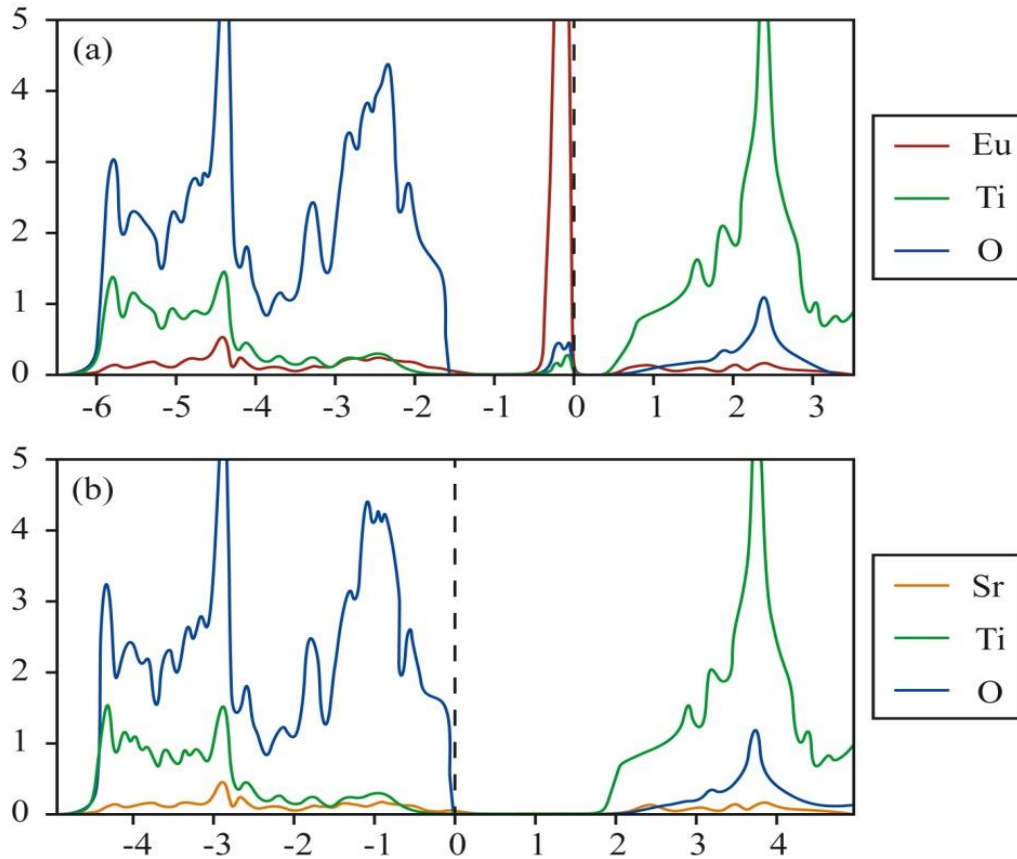
Eu^{2+}

4f localized electrons
AFM ordering at 5.3 K
Strong spin-lattice coupling

Competing Instabilities in EuTiO_3 , *PRL* **110**, (2013) 027201.

Antiferrodistortive phase transition in EuTiO_3 , *Phys. Rev. B* **86**, 054112 (2012)

Localized Eu 4f electron band

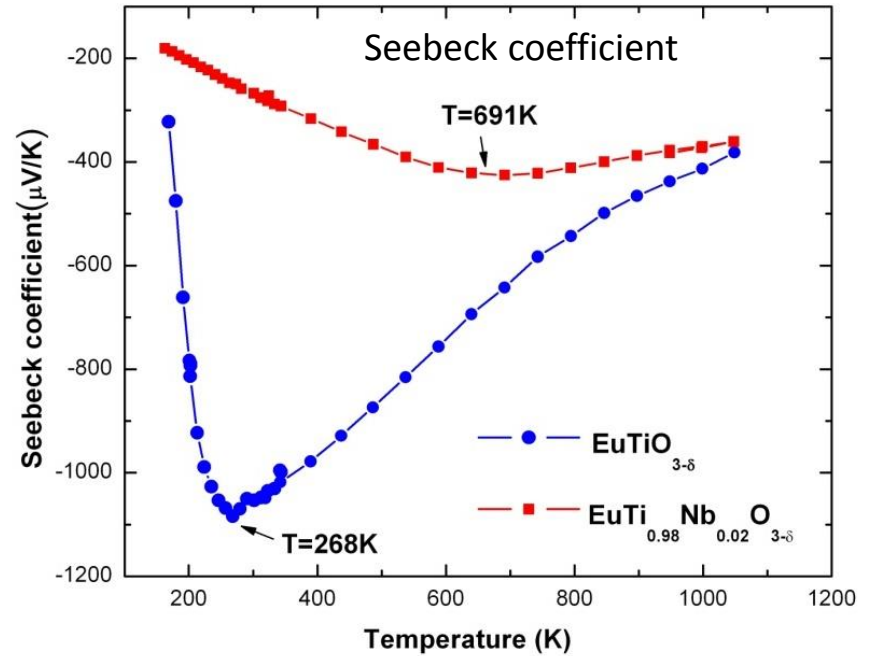
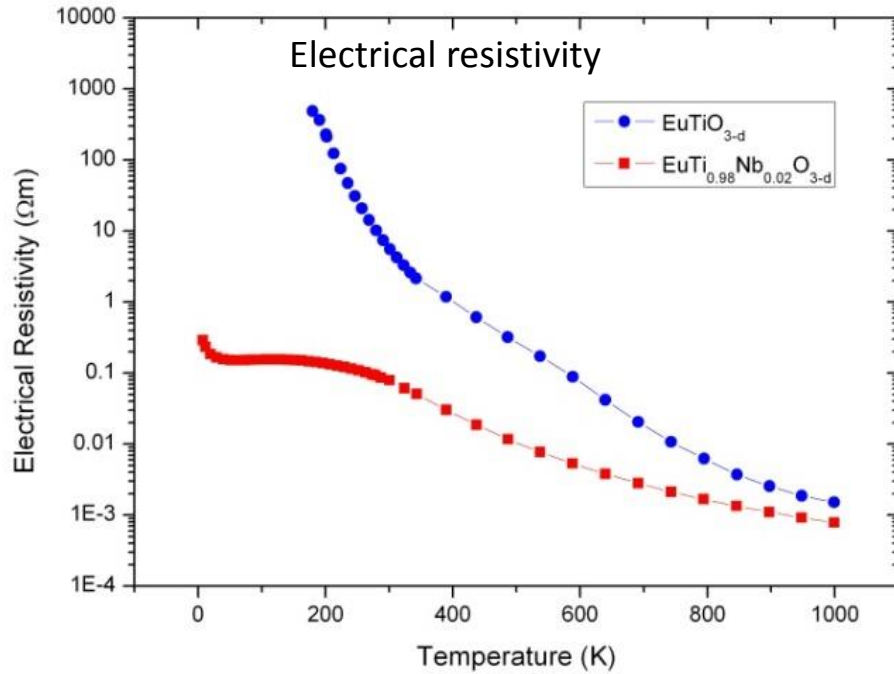


EuTiO₃

- Band gap < 1 eV
 - Localized Eu 4f electron band near the Fermi level → high Seebeck coefficient
- $$S \propto [\partial \ln n(E) / \partial E]_{E=E_F}$$

Vienna *ab-initio* Simulation Package (VASP) code, Heyd-Scuseria-Ernzerhof (HSE) hybrid functional

Thermoelectric properties of $\text{EuTiO}_{3-\delta}$ & $\text{EuTi}_{0.98}\text{Nb}_{0.02}\text{O}_{3-\delta}$



- Decrease of σ by Nb 2% substitution: one order of magnitude at high T

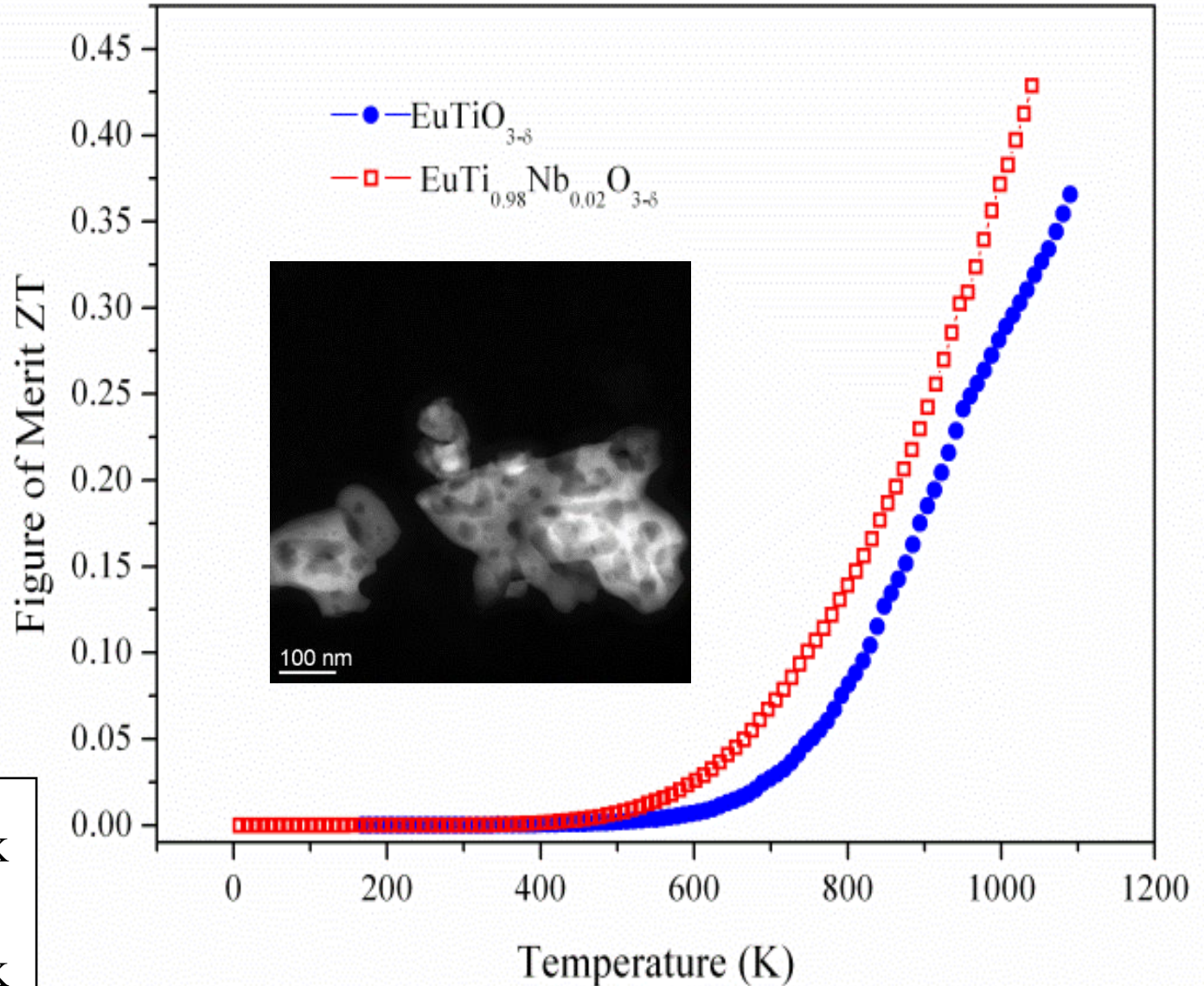
- EuTiO_3 is one of the oxides with highest $|S| = 1081 \mu\text{V/K}$ at $T = 268\text{K}$

-> n-type thermoelectric leg material

EuTiO₃: One of the best perovskite-type TE materials

Figure of Merit:

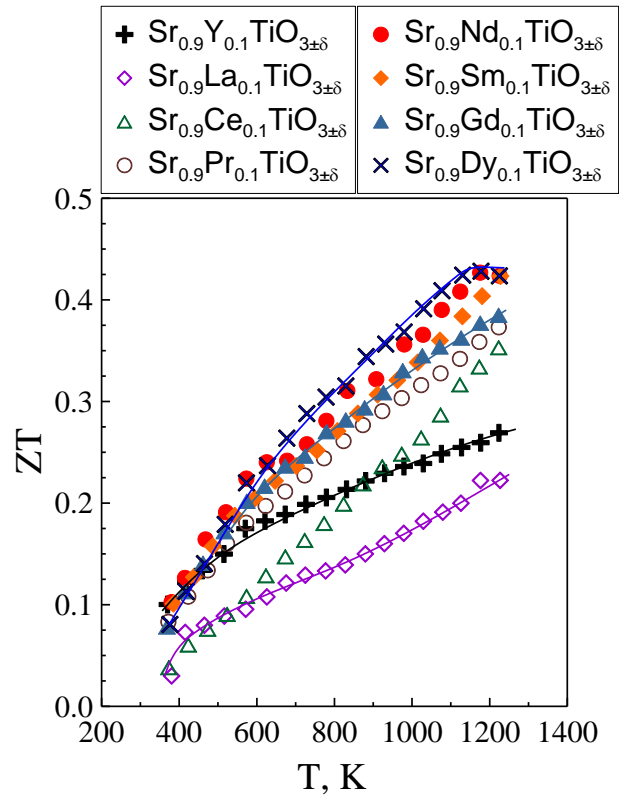
$$ZT = \frac{S^2 \sigma}{\kappa} T$$



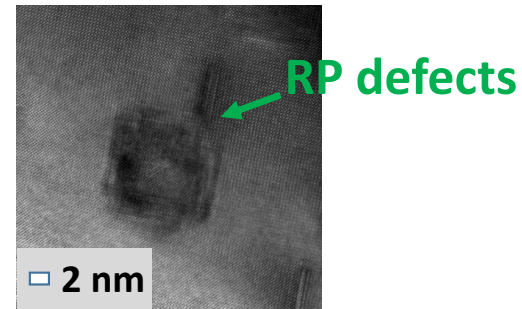
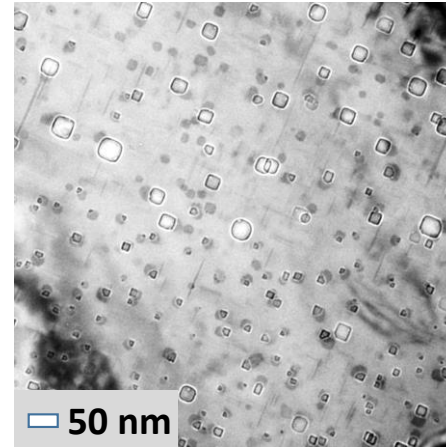
EuTi_{0.98}Nb_{0.02}O₃
ZT = 0.43 at T = 1040 K

EuTiO₃
ZT = 0.37 at T = 1090 K

$\text{Sr}_x\text{Ln}_{1-x}\text{TiO}_{3-\delta}$ Perovskite-type thermoelectric titanates



A. V. Kovalevsky, et al, *Phys. Chem. Chem. Phys.*, **16**, (2014) 26946-26954



A. Kovalevsky, A. Yaremchenko, M. Aguirre, S. Populoh, S. Patrício, J. Macías, A. Weidenkaff, J. Frade

BaTiO₃

Band gap: ~ 3.2 eV

Ferroelectric, piezoelectric,
dielectric, thermoelectric,...



ferromagnetic
Ferroelectric
.....

EuTiO₃

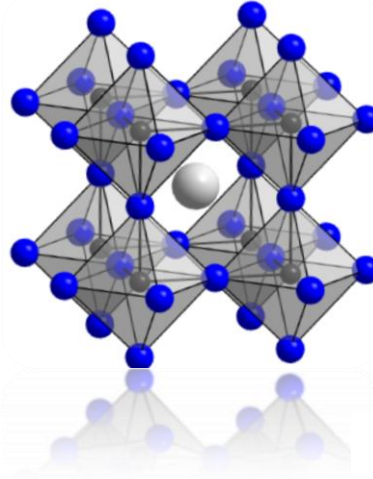
Band gap: ~ 1 eV

Magnetic, dielectric,
incipient ferroelectric,
Huge Seebeck,...

Thermoelectric ?

BTO as thermoelectric:

- low electric conductivity
- low lattice thermal conductivity
- abundant elements

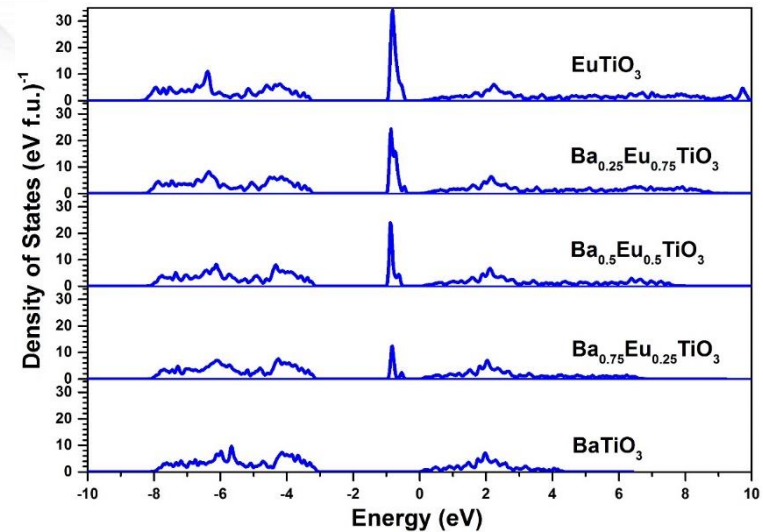


ETO as thermoelectric:

- high electric conductivity
- high lattice thermal conductivity
- rare earth element
- band structure: localised Eu 4f

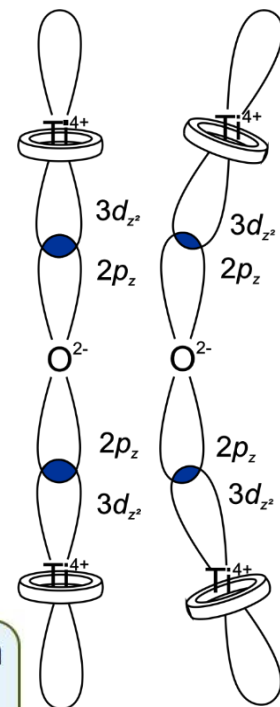
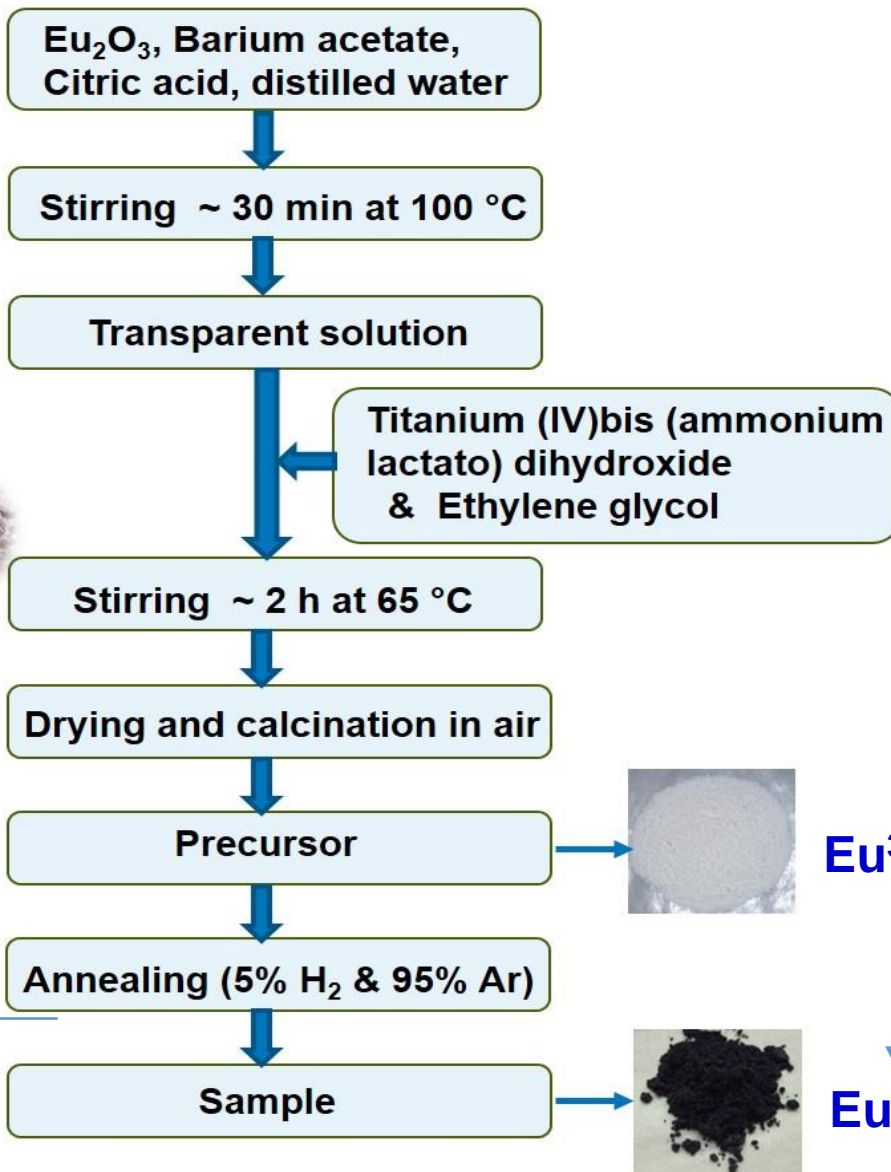
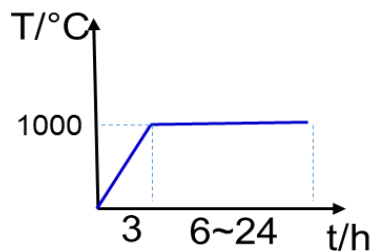
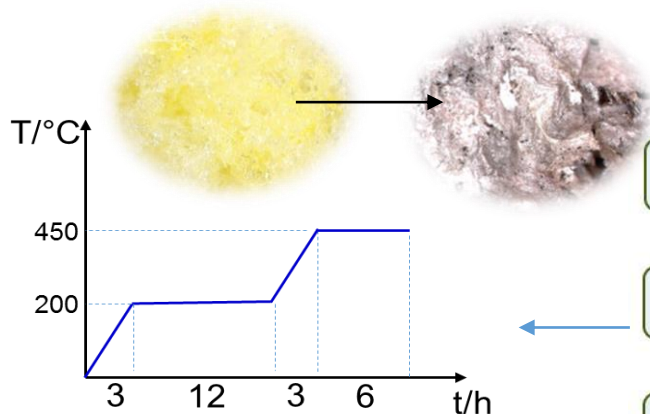
Similarities of BTO & ETO:

- n-type semiconductor
- high Seebeck coefficient
- high temperature stability
- flexible perovskite structure



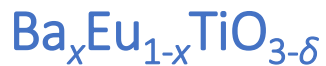
Synthesis: $\text{Ba}_{1-x}\text{Eu}_x\text{TiO}_3$

Eu_2O_3 dissolves in hot water

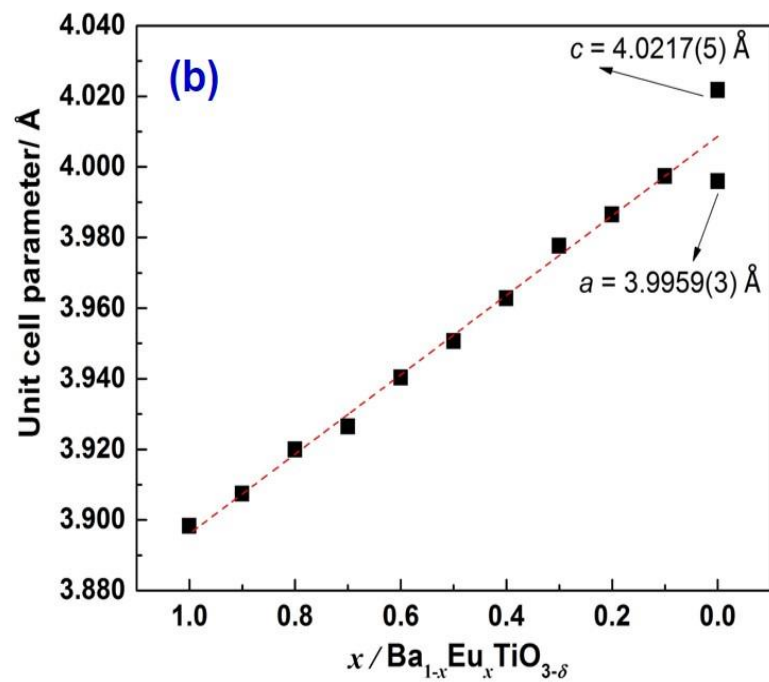
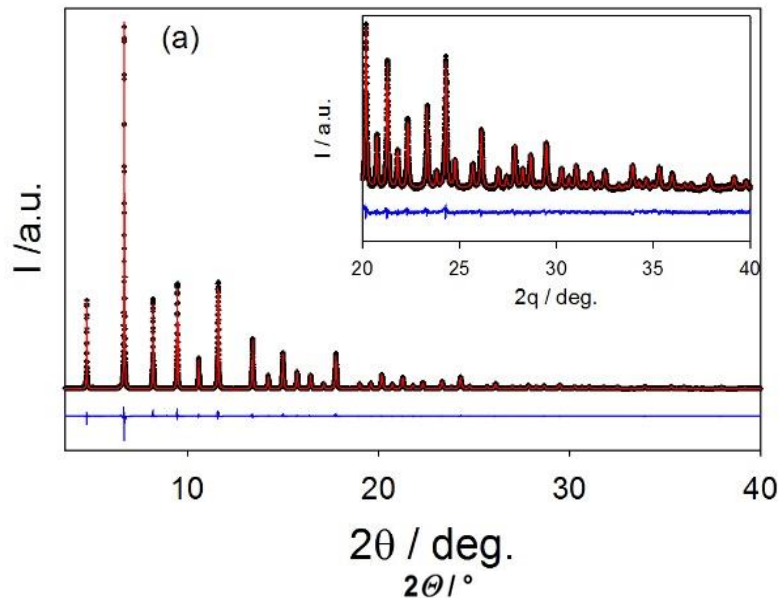


Eu^{3+}

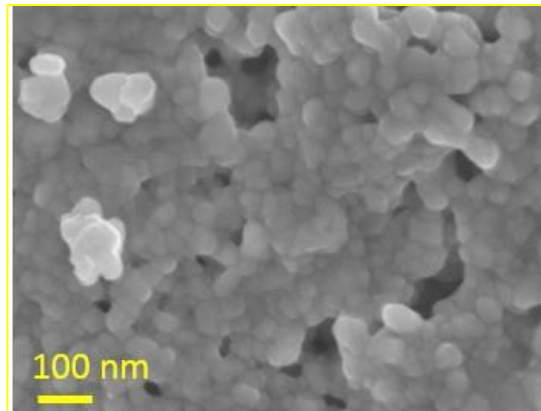
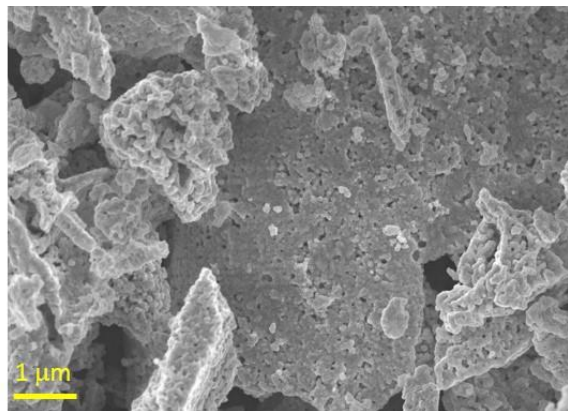
Eu^{2+}



Unit cell parameters as function of the Eu concentration



Vegard's law: distances of the nearest-neighbor ions become shorter due to the contraction of the unit cell

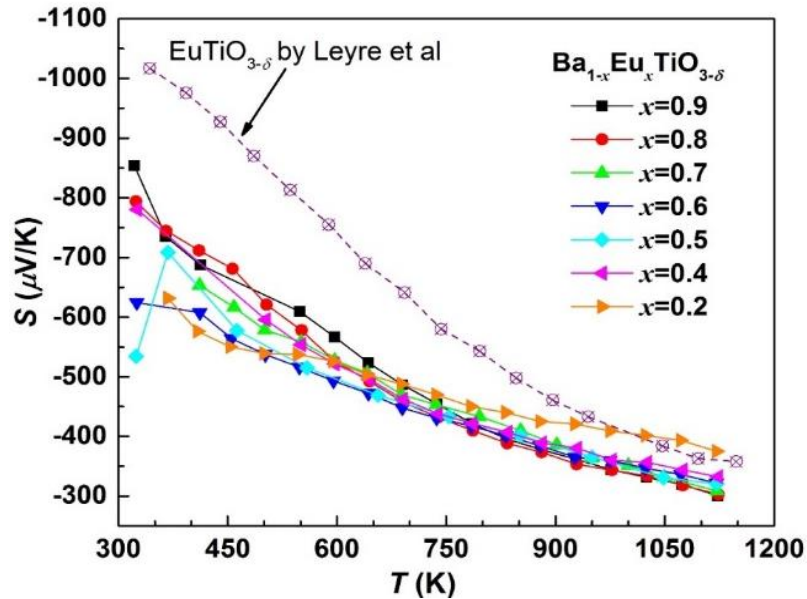


homogeneous morphology
with particle size **~ 40 nm**.



X. Xiao et al, *PCCP*, in press

Seebeck coefficient of $\text{Ba}_{1-x}\text{Eu}_x\text{TiO}_{3-\delta}$



high T limit: Heikes formula

$k_B T \ll U_0$ on-site repulsion ($U_0 = 0.1 \sim 1$ eV)

$$S(T \rightarrow \infty) = \frac{-k_B}{e} \ln \frac{2(1-n)}{n}$$

n = carriers per unit cell

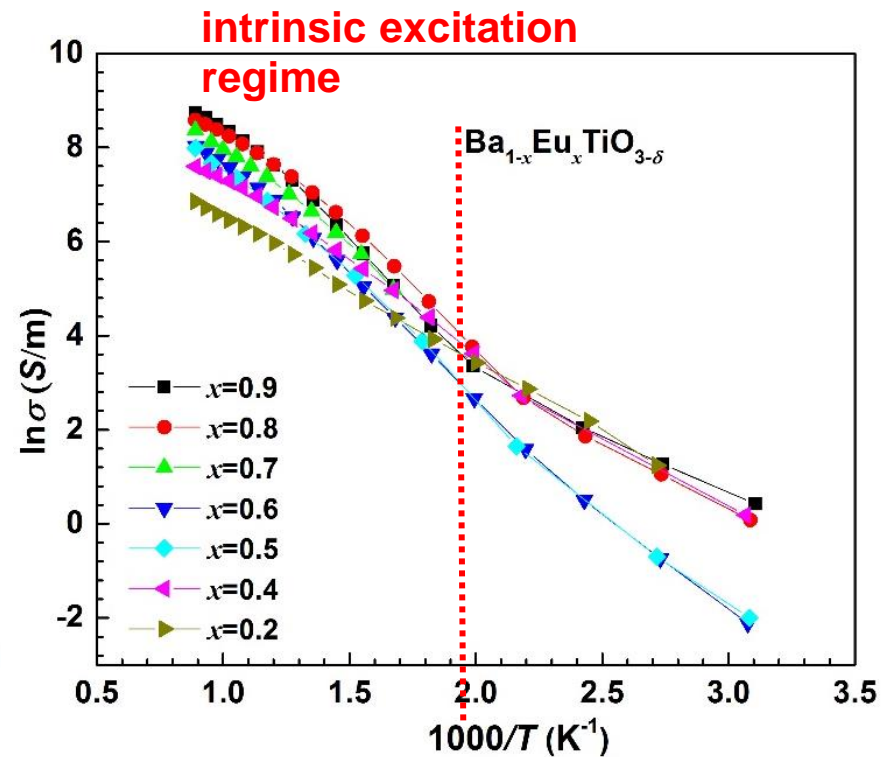
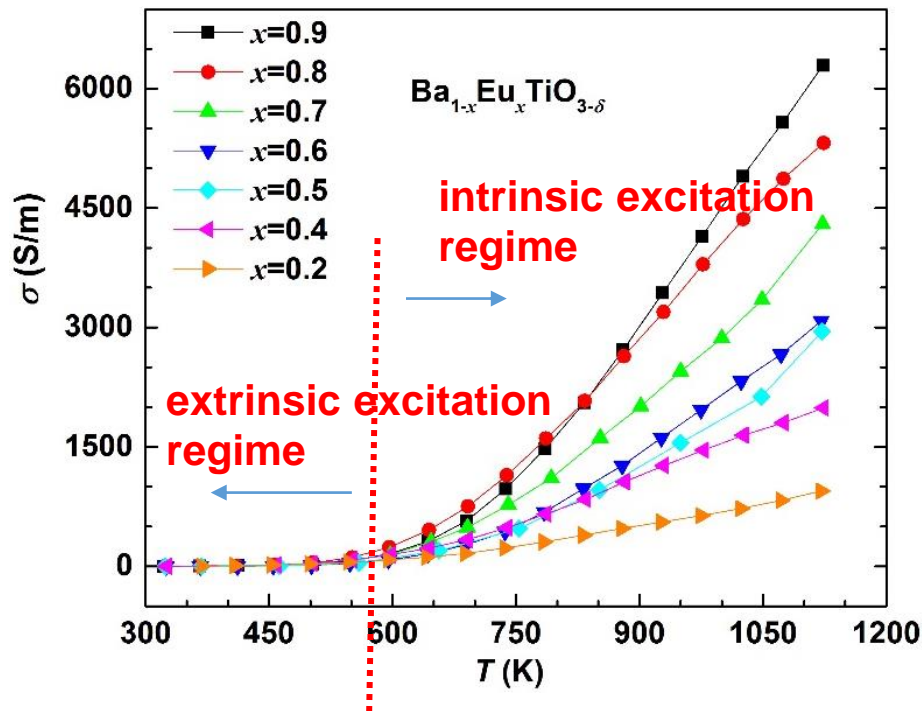
P. M. Chaikin et al. Phys. Rev. B 13, 647 (1976)

❖ low temperature: no well-defined relation between Eu content and S value;

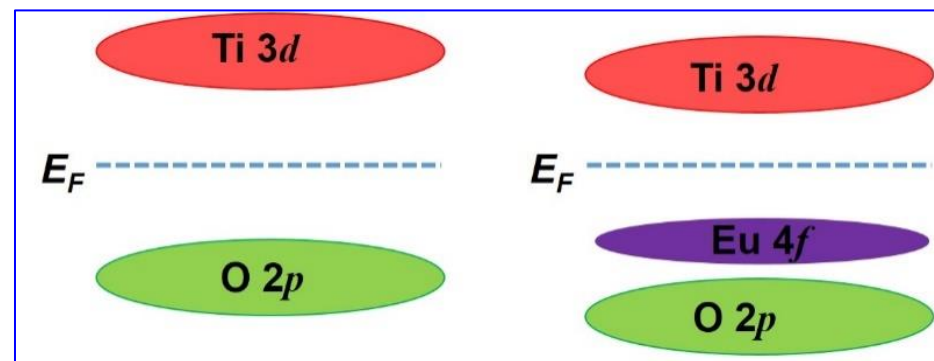
❖ high temperature ($T > 1000$ K): the $|S|$ value decreases with Eu content.

Samples No.	$\sigma_{1123\text{K}}$ (S/m)	E_A (eV)	$S_{1123\text{K}}$ ($\mu\text{V/K}$)	E_s (eV)	W_p (eV)	$n_{1123\text{K}}$ ($\times 10^{20} \text{cm}^{-3}$)	μ ($\text{cm}^2\text{V}^{-1}\text{s}^{-1}$)
$x = 0.2$	945	0.24	-375	0.18	0.12	4.0	0.15
$x = 0.4$	1990	0.24	-332	0.23	0.02	6.5	0.19
$x = 0.5$	2948	0.33	-320	0.30	0.06	7.5	0.25
$x = 0.6$	3081	0.32	-321	0.24	0.16	7.5	0.26
$x = 0.7$	4300	0.29	-308	0.34	-	8.7	0.31
$x = 0.8$	5317	0.26	-302	0.27	-	9.3	0.35
$x = 0.9$	6289	0.30	-300	0.30	-	9.6	0.41

Electrical conductivity of $\text{Ba}_{1-x}\text{Eu}_x\text{TiO}_{3-\delta}$

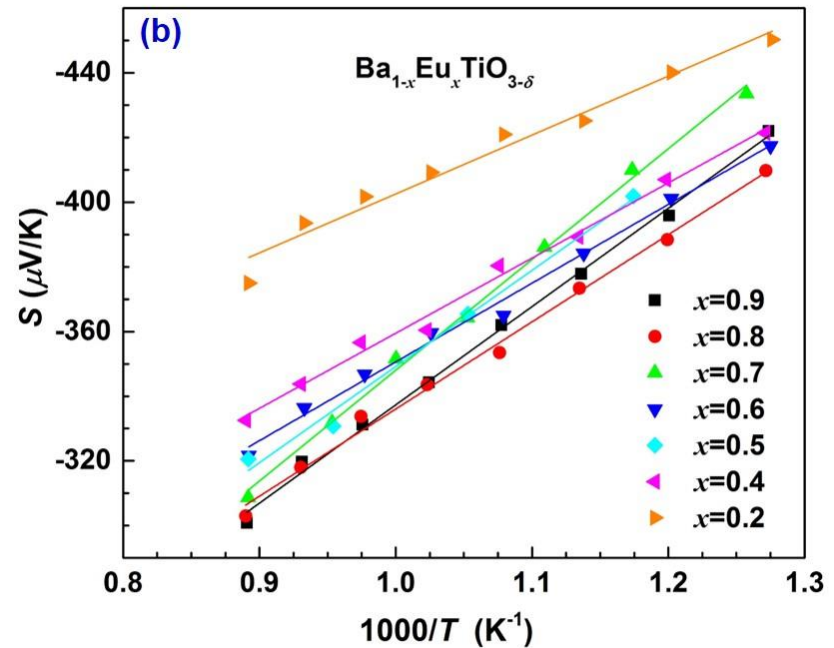
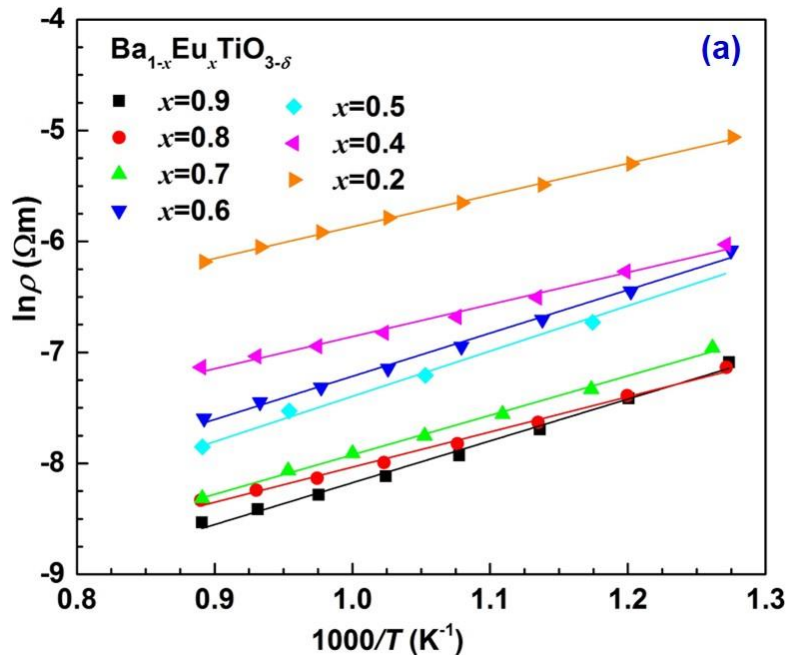


Eu 4f electrons are excited into the conduction band and dominate the electron transport properties at high temperature.



schematic diagram of the band structure of BTO and ETO.

Electron transport mechanism of $\text{Ba}_{1-x}\text{Eu}_x\text{TiO}_{3-\delta}$



$\ln \rho$ and S as a function of $1000/T$

Arrhenius formula:

$$\rho(T) = \rho_0 \exp\left(\frac{E_A}{k_B T}\right) \rightarrow E_A$$

Mott's adiabatic small polaron conduction model:

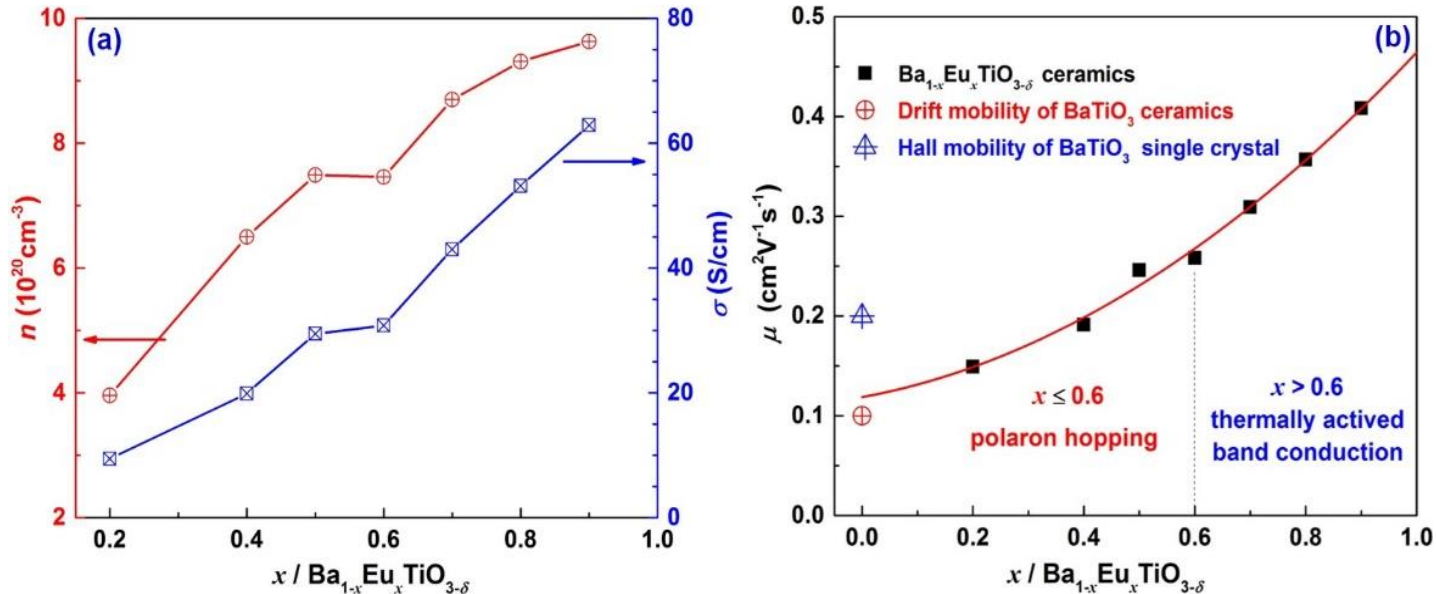
$$S = \frac{k_B}{e} \left(\frac{E_S}{k_B T} + r \right) \rightarrow E_S$$

$E_A > E_S$: thermally activated hopping

hopping binding energy:

$$W_p = 2(E_A - E_S)$$

Electron transport mechanism of $\text{Ba}_{1-x}\text{Eu}_x\text{TiO}_{3-\delta}$



(a) The charge carrier concentration (n), electrical conductivity (σ) and (b) carrier mobility (μ) as a function of Eu-content (x) at 1123 K.

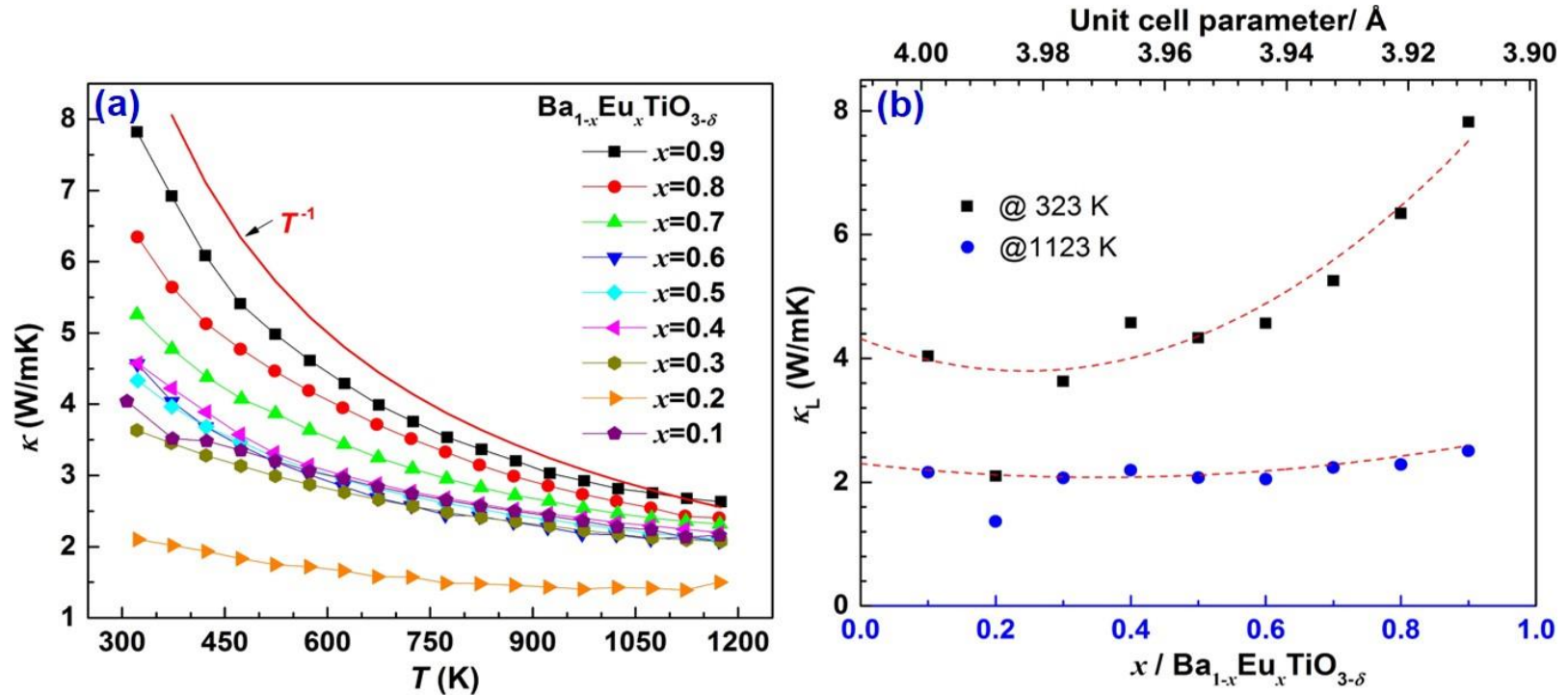
❖ $x \leq 0.6$, $E_A > E_S$

dominated conducting mechanism belongs to polaron hopping conduction.

❖ $x > 0.6$, thermally activated band conduction ?

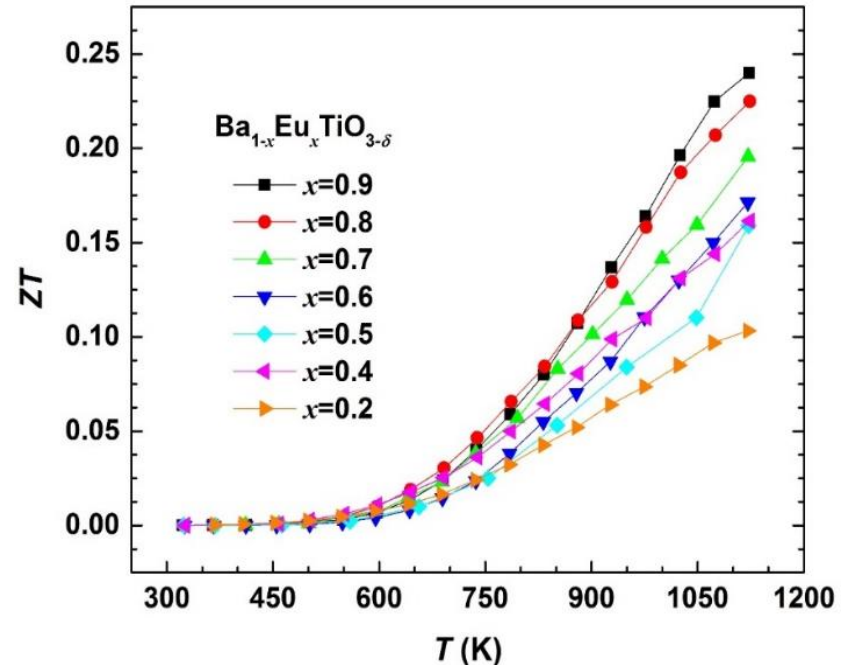
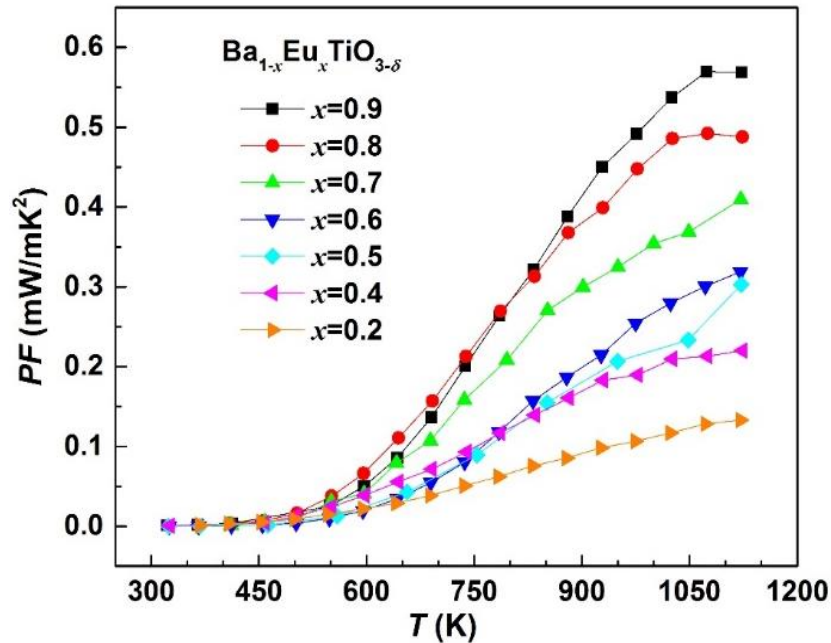
Samples No.	$\sigma_{1123 \text{ K}}$ (S/m)	E_A (eV)	$S_{1123 \text{ K}}$ ($\mu\text{V}/\text{K}$)	E_S (eV)	W_p (eV)	$n_{1123 \text{ K}}$ ($\times 10^{20} \text{ cm}^{-3}$)	μ ($\text{cm}^2 \text{ V}^{-1} \text{ s}^{-1}$)
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Thermal conductivity of $\text{Ba}_{1-x}\text{Eu}_x\text{TiO}_{3-\delta}$



- ❖ κ follows a T^{-1} dependence, indicating the dominant phonon scattering mechanism is the **Umklapp scattering** (phonon–phonon interactions).
- ❖ Eu substitution decreases the Ti–O distance, strengthening the Ti–O bond, resulting in higher κ_L .
- ❖ In this studied system, the changes in the bond strength appear to be more effective for depressing the thermal conductivity than the simultaneously occurring point defect scattering.

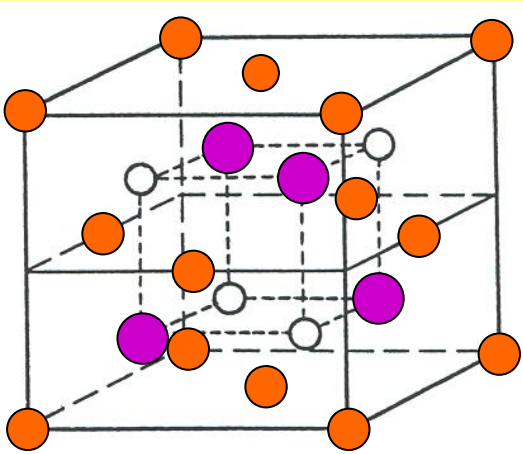
Power factor & ZT value of $\text{Ba}_{1-x}\text{Eu}_x\text{TiO}_{3-\delta}$



- ❖ **Eu** substitution significantly **enhances** the *Power factor* and the *ZT value*, resulting from that Eu substitution causes a particularly strong improvement in **electrical conductivity**.
- ❖ $\text{Eu}_{0.9}\text{Ba}_{0.1}\text{TiO}_3$ $ZT = 0.24$ at 1122 K

Intermetallics: half-Heusler compounds

n-type TiNiSn, p-type TiCoSb



- M=Ti, Zr, Hf
- Ni/Co
- Sn/Sb

Four fcc sublattices shifted $\frac{1}{4}$ along (111).

A (0,0,0) occupied by Ni/Co

B ($\frac{1}{4}, \frac{1}{4}, \frac{1}{4}$) occupied by M

C ($\frac{3}{4}, \frac{3}{4}, \frac{3}{4}$) occupied by Sn/Sb

narrow bands

high effective mass

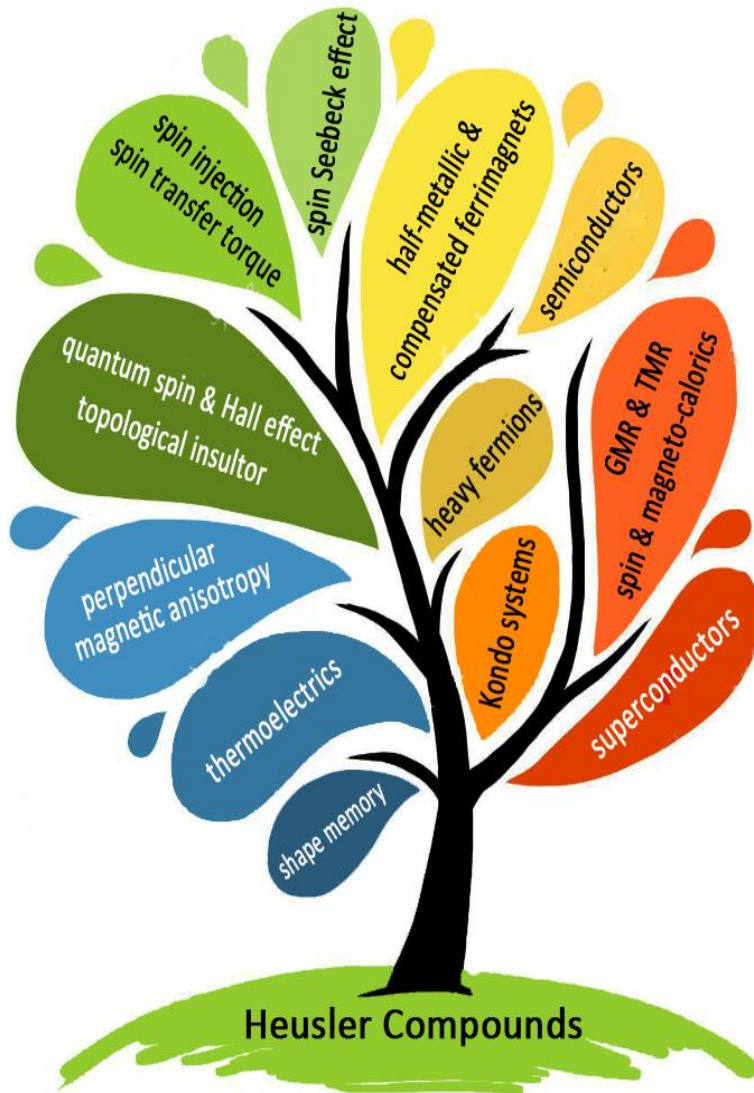
a large Seebeck coefficient

high thermal conductivity

TiNiSn: ~10-20 W/mK

commercial Bi_2Te_3 : ~1-2 W/mK

Properties and functions of Heusler compounds



Permanent magnets

Multiferroics

Piezoelectrics

Thermoelectrics

Photovoltaics

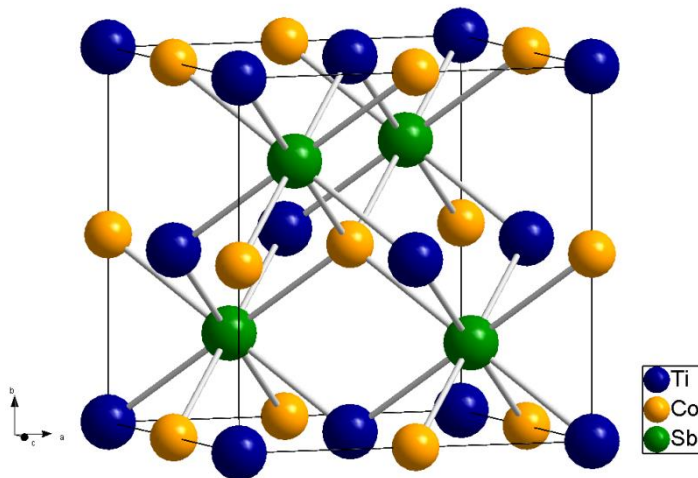
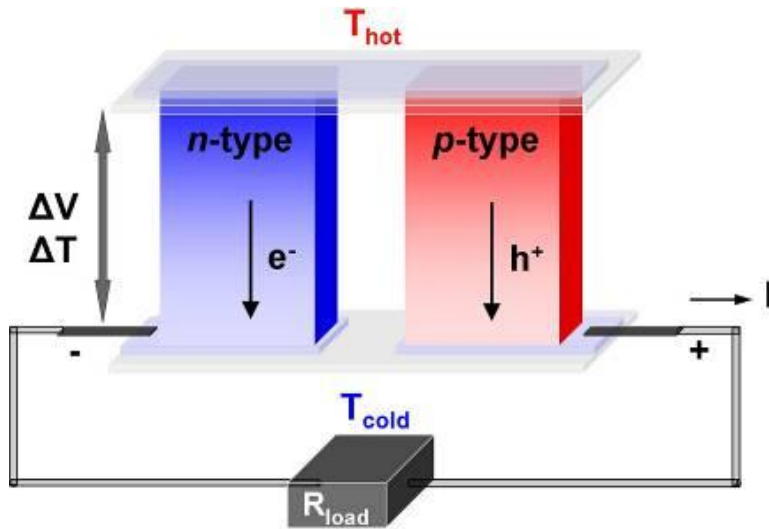
p-type transparent conductors

Superconductors

Topological insulators

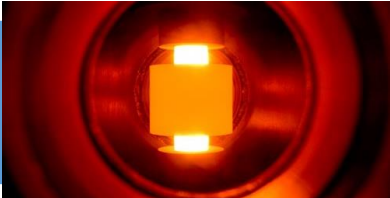
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TE-HH: Synthesis methods



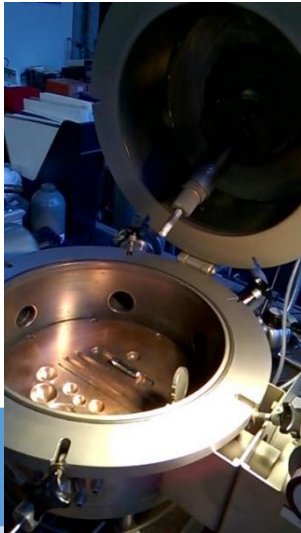
Mixing metals/Arc melting/annealing

Induction/MW melting 

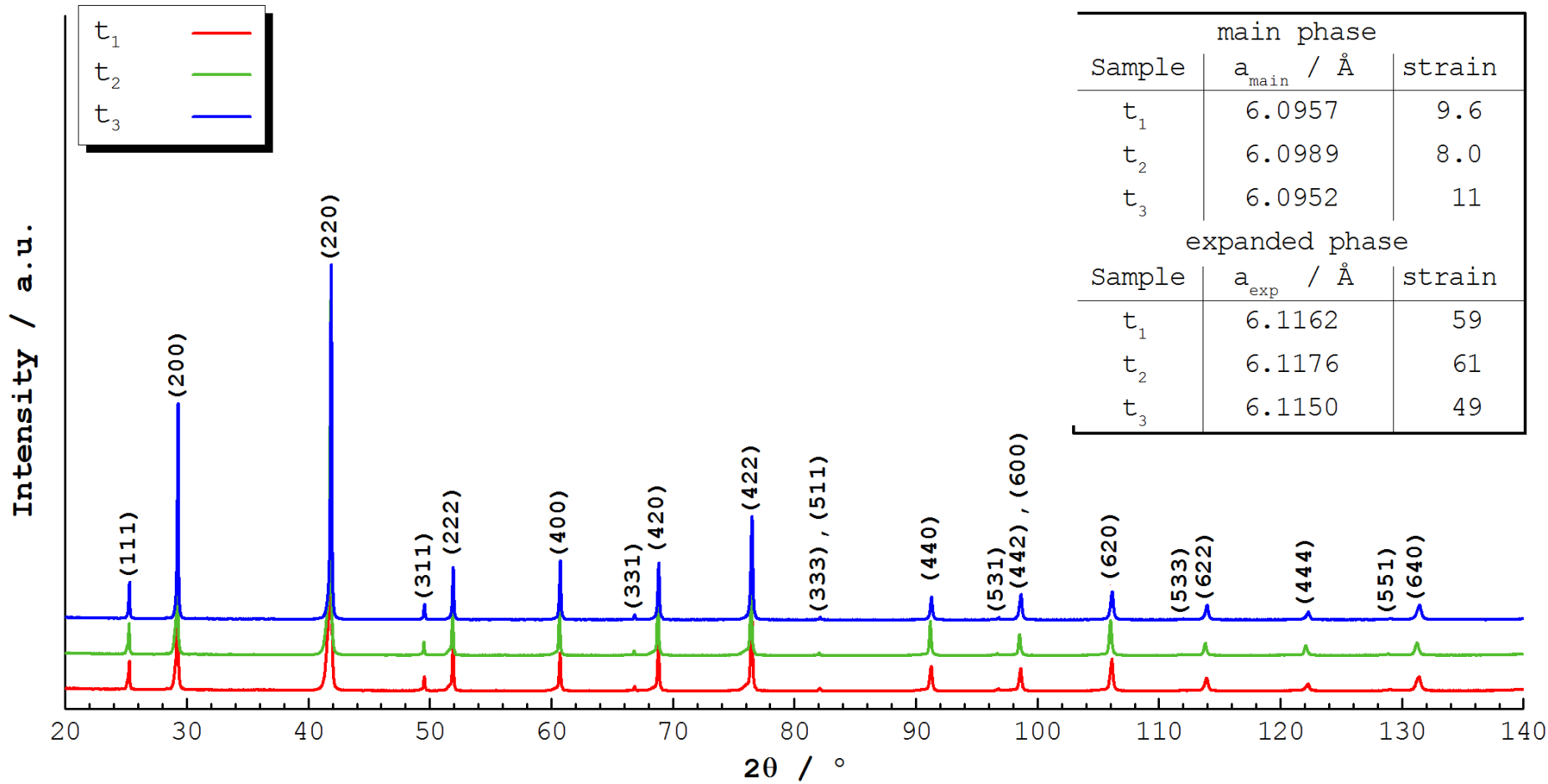
SPS 

Polishing 

Cutting 

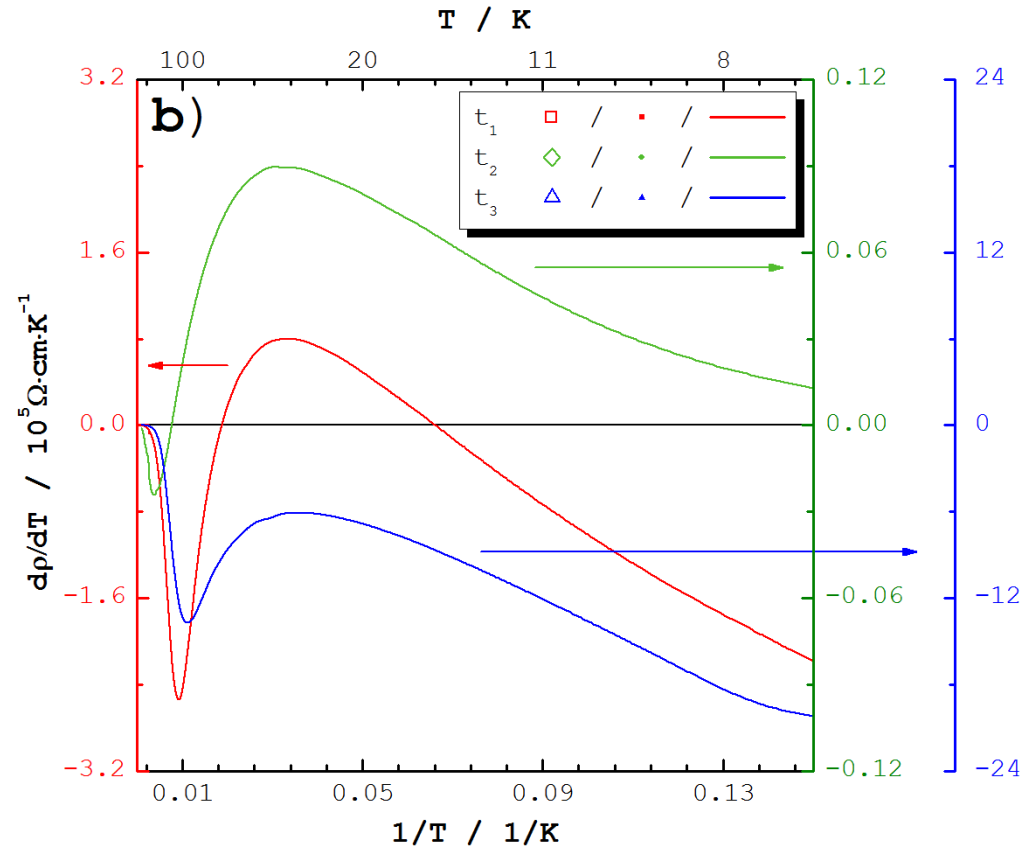
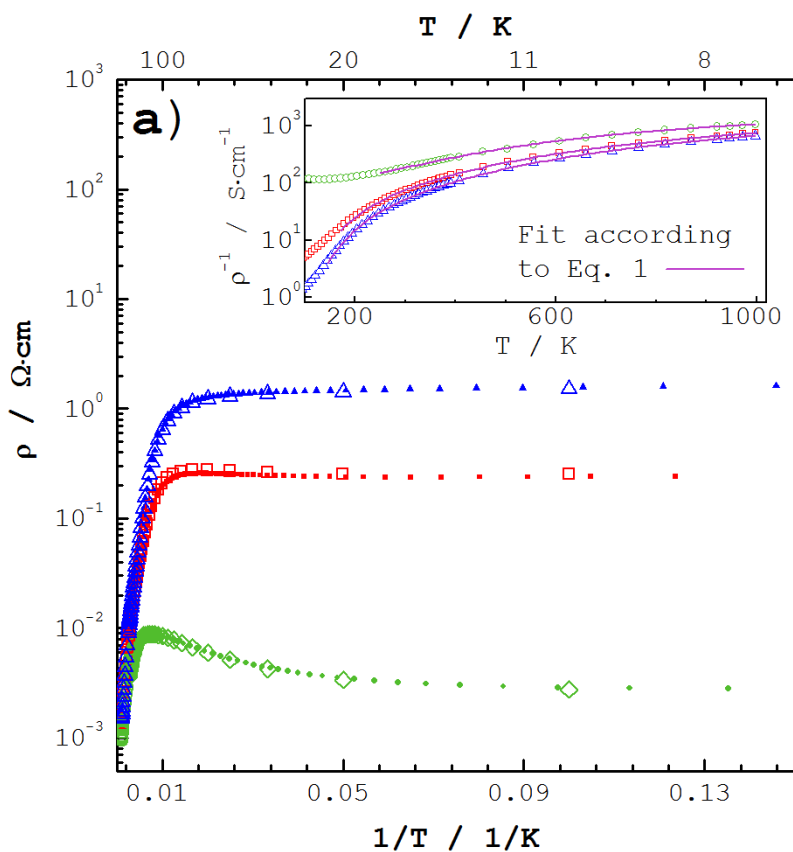


XRD : $\text{Zr}_{0.43}\text{Hf}_{0.57}\text{NiSn}$



- Diffusion $t_1 = 8$ min, $t_2 = 32$ min; $t_3 = 72$ min
- Main phase: half-Heusler
- Expanded phase with the same symmetry.

Electrical resistivity of $\text{Zr}_{0.43}\text{Hf}_{0.57}\text{NiSn}$

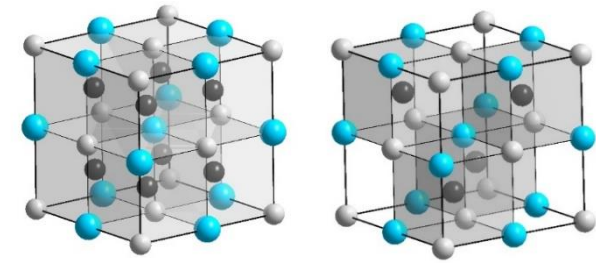


	Sample		
Parameters	t_1	t_2	t_3
T range (K)	170 – 998	250 – 998	145 – 998
ΔE_0 (meV)	330 ± 8	233 ± 6	349 ± 5
ΔE_1 (meV)	108 ± 2	26 ± 2	118 ± 1

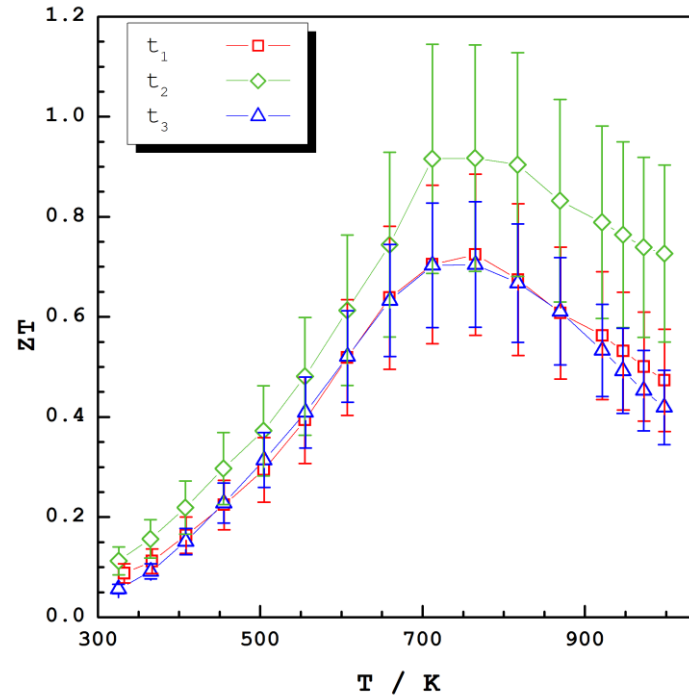
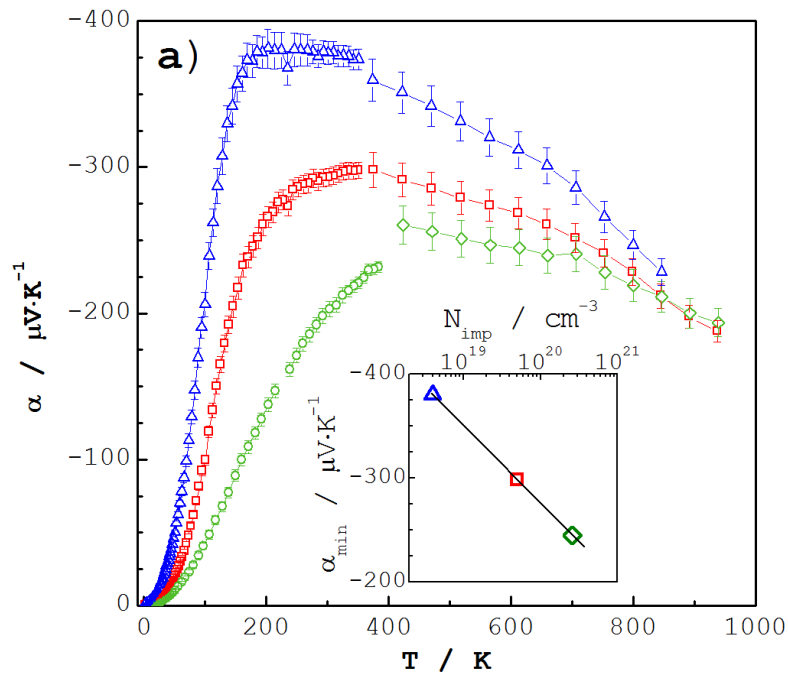
- Intrinsic behaviour at high-T
- Presence of an impurity level
- Metallic behaviour at low-T

Half-Heusler phases defect control: $\text{Ti}_{0.37}\text{Zr}_{0.37}\text{Hf}_{0.26}\text{NiSn}$

- impurity band merge with conduction band.
- modification of the DOS near the edge of the conduction band enhance charge carrier concentration



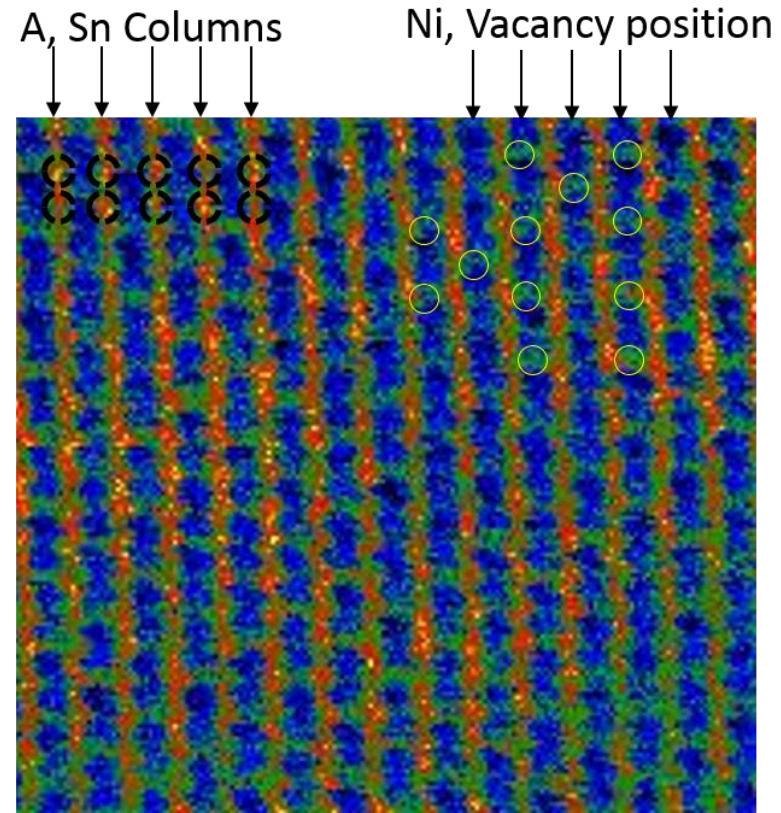
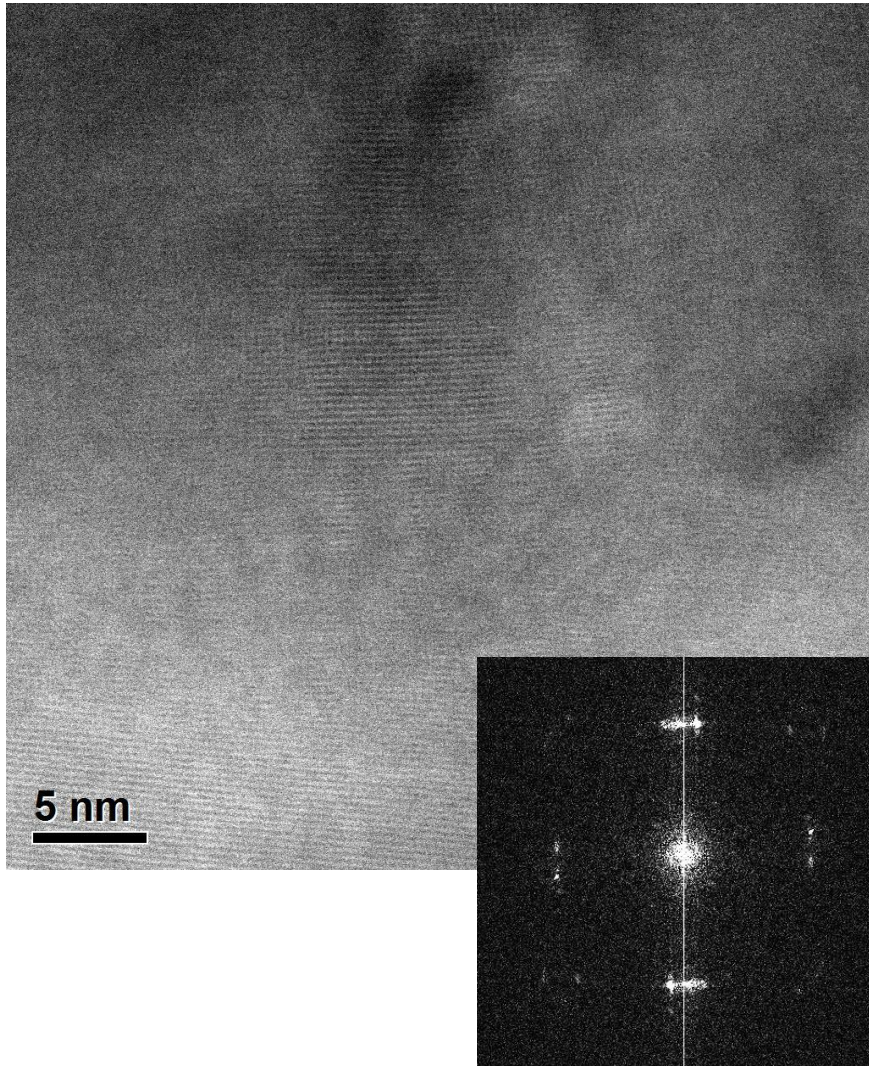
Half-Heusler (XYZ)



Interstitial Ni defects act as classical dopants – control of n

K. Galatzka et al, in preparation

FH nanoprecipitates in HH matrix



HRSTEM with HAADF in aberration corrected TEM (Titan G3 at 300 keV) by Myriam Aguirre, Zaragoza

Summary and Conclusions

New materials :

- ✓ band gap and defect control by innovative **synthesis** processes
- ✓ large thermopower in **correlated electronic systems**
 - Giant Seebeck in EuTiO_3 ($S > 1000 \mu\text{V/K}$)
- ✓ low thermal conductivity by **hindering phonon** transp. on grain boundaries
 - synthesis method for titanate nanocubes and foams
- ✓ thermoelectric conversion at **$T > 700^\circ\text{C}$ in air** demonstrated
 - high T thermoelectric conversion: power output improved 10 times

Acknowledgements

Collaborations: Ryoji Funahashi, Andrei Kovalevski, Jiri Hejtmánek, Joachim Maier, Aldo Steinfeld, ...

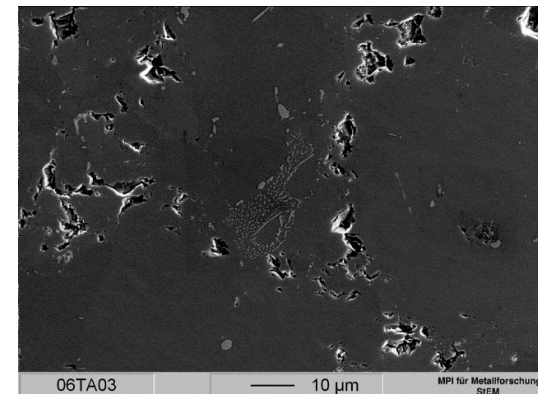
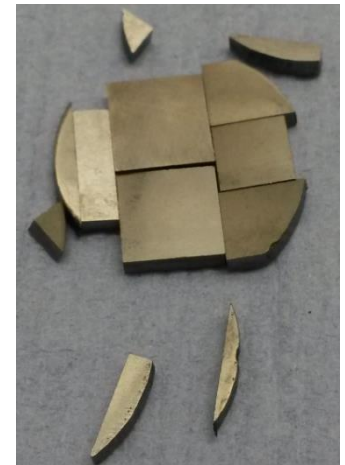
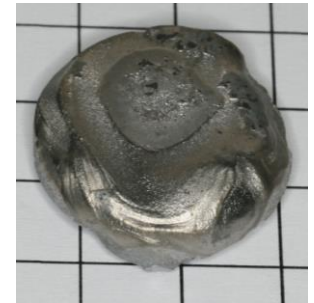
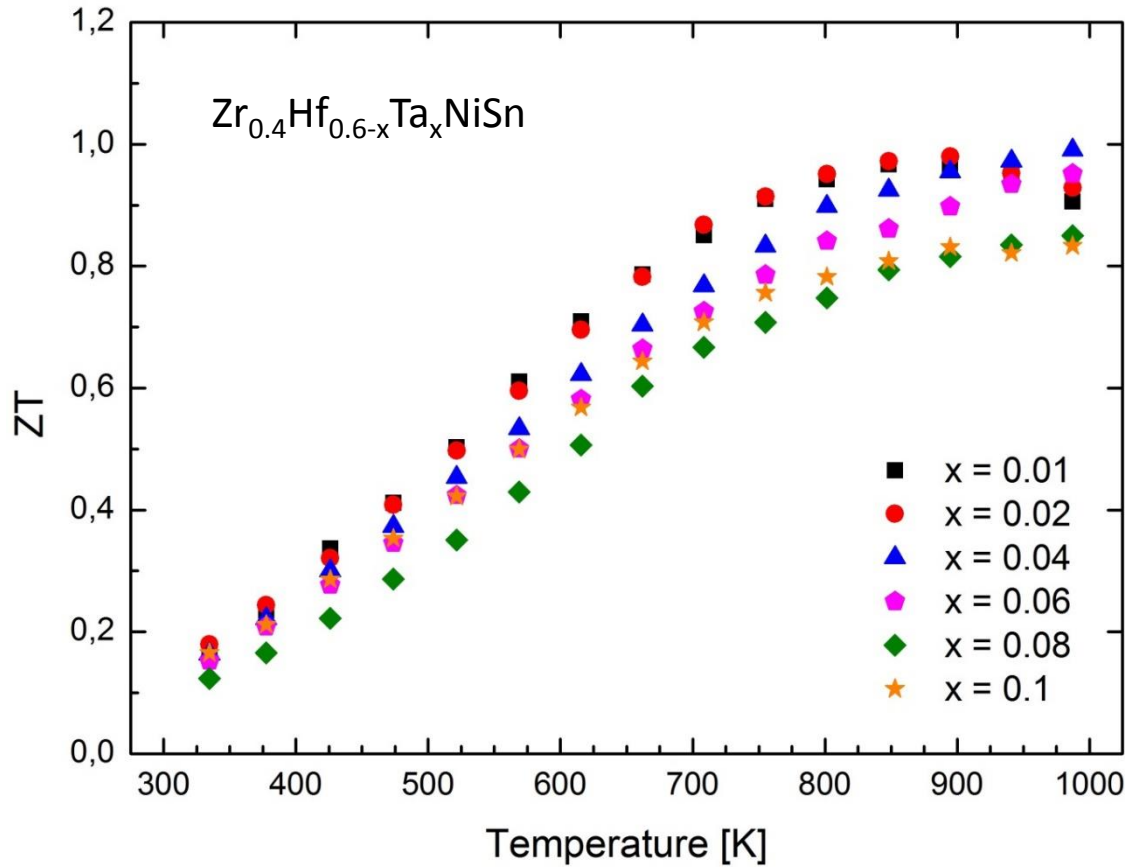
Funding: DfG, BmBF, BW, SNF, Vector

Beamtime: **ESRF**, **SINQ**



Zr_{0.4}Hf_{0.6-x}Ta_xNiSn Half-Heusler Compounds

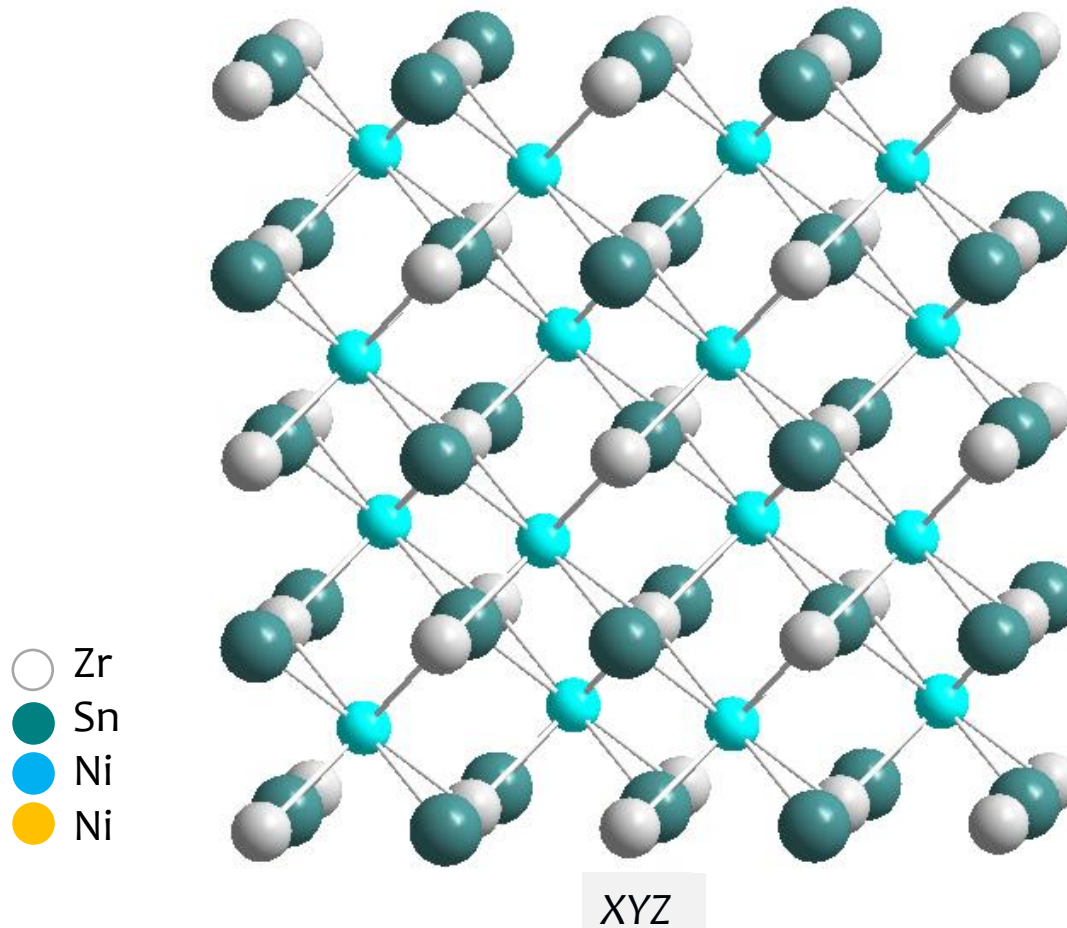
reduce Hf content



Full Heusler/Half Heusler compounds

T. Graf et al., Prog. Solid State Chem., vol. 39, pp. 1–50, 2011

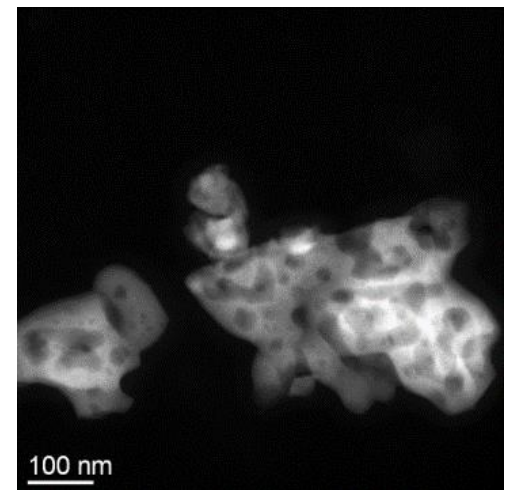
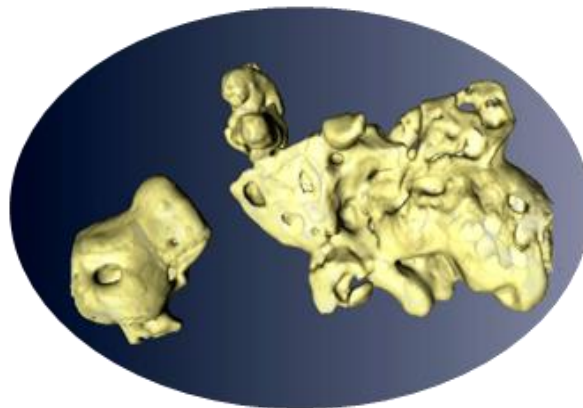
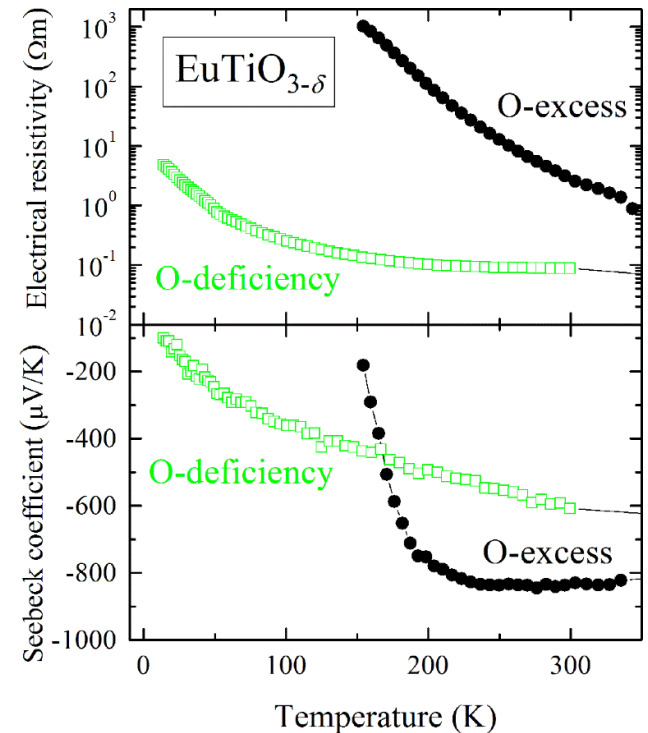
Heusler structure, $Fm\bar{3}m$ symmetry \leftrightarrow Half-Heusler structure, $F\bar{4}3m$ symmetry



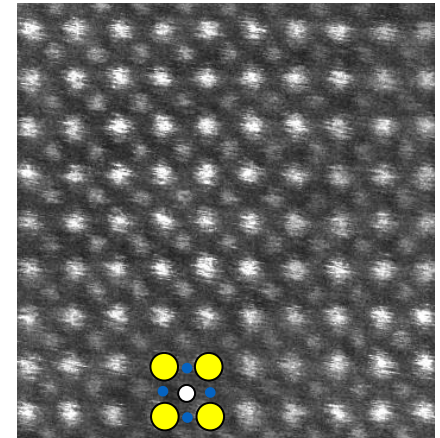
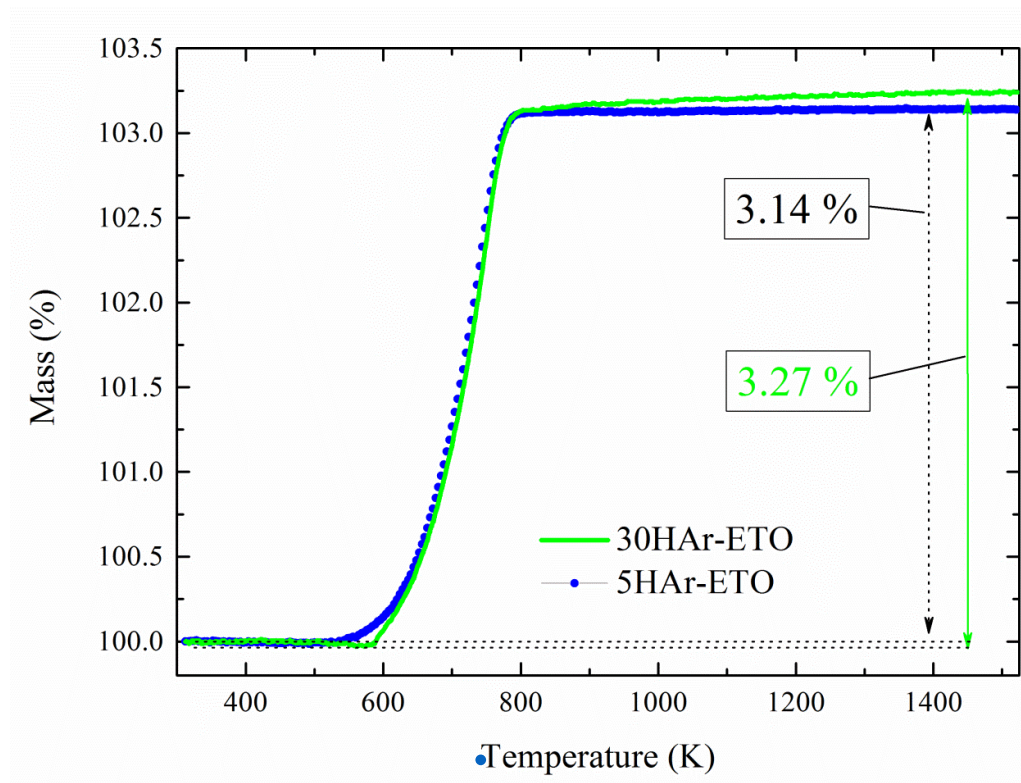
Removing 4a Ni atoms per unit cell = change of symmetry

$\text{Sr}_x\text{Ln}_{1-x}\text{TiO}_{3-\delta}$

- EuTiO_3 : **Sr for Eu** substitution up to $x = 0.75$ has no detrimental effect on the TE properties
- strong **hybridization** of the localized Eu $4f$ states with the delocalized Ti $3d$ states
- reduced titanates possess up to 5 orders of magnitude lower electrical **resistivity**, confirming that oxygen vacancies act as electron donors
- **Soft chemistry** synthesis method for nanostructured titanates
 κ from $>7 \text{ W K}^{-1} \text{ m}^{-1}$ to $<2.5 \text{ W K}^{-1} \text{ m}^{-1}$



Oxygen content of titanates



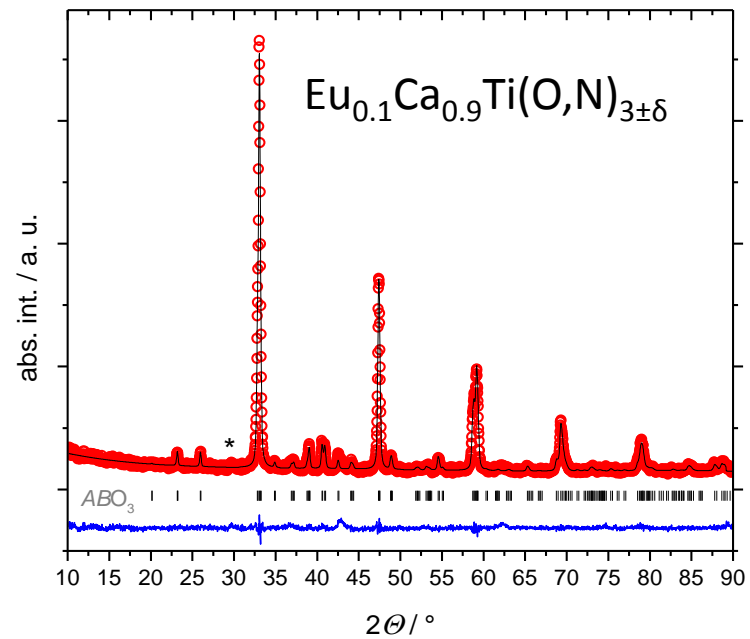
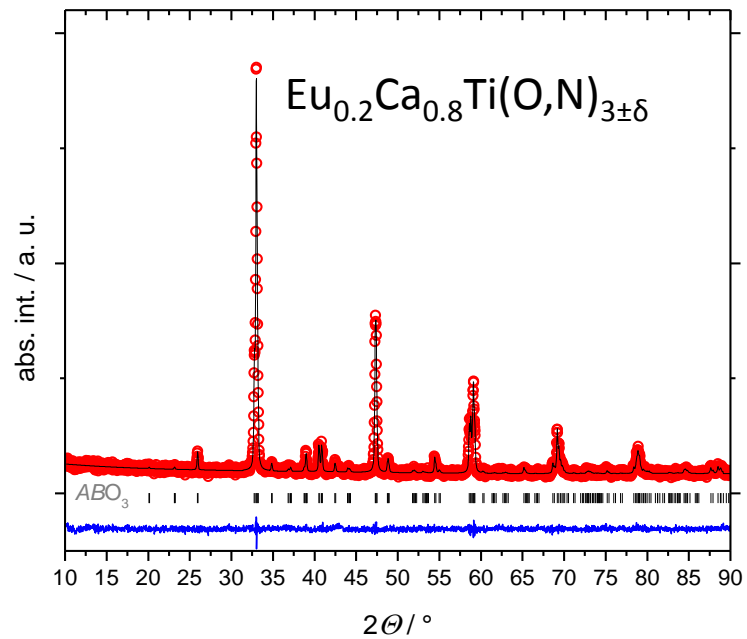
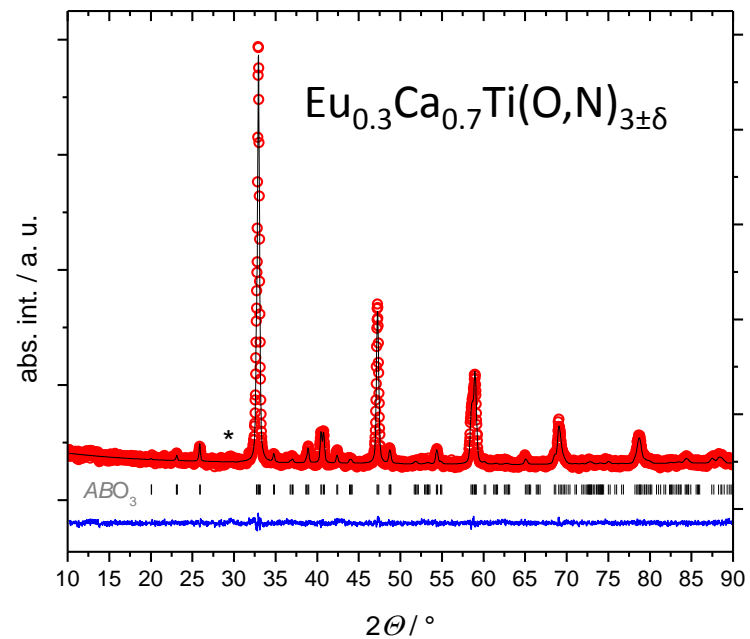
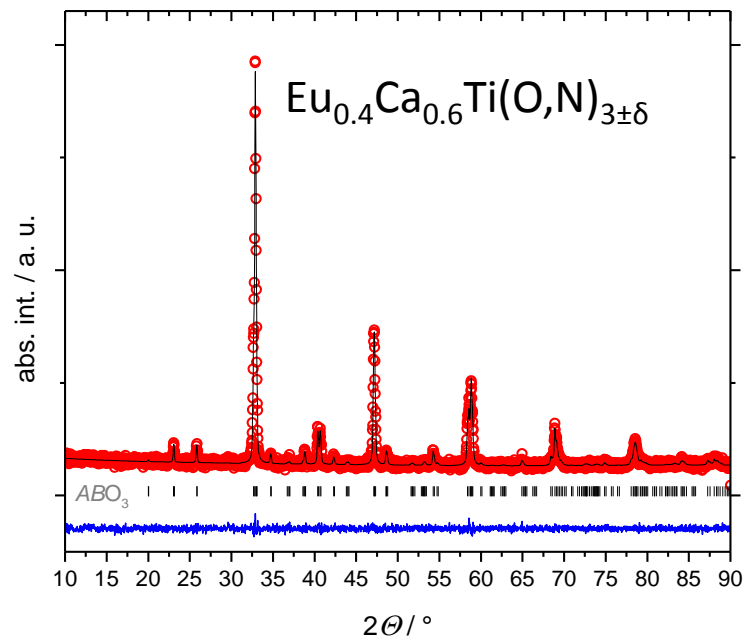
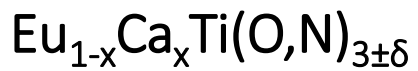
● Sr/Eu
○ Ti
● O

30HAr-ETO: $\delta = 0.007(5)$

$\text{EuTiO}_{2.993(5)}$ slight O-deficiency

5HAr-ETO: $\delta = -0.013(3)$

$\text{EuTiO}_{3.013(3)}$ slight O-excess



X-ray Photoelectron Spectroscopy (XPS)

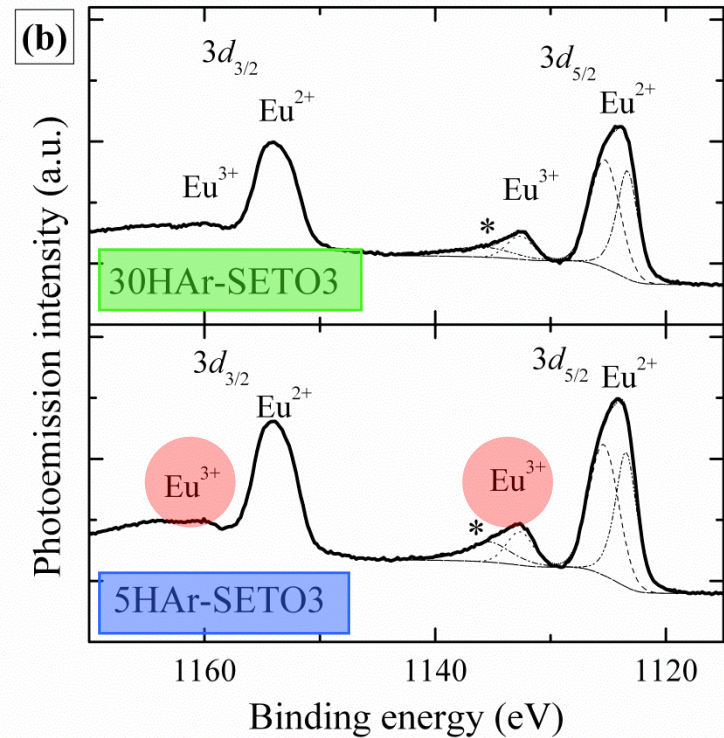
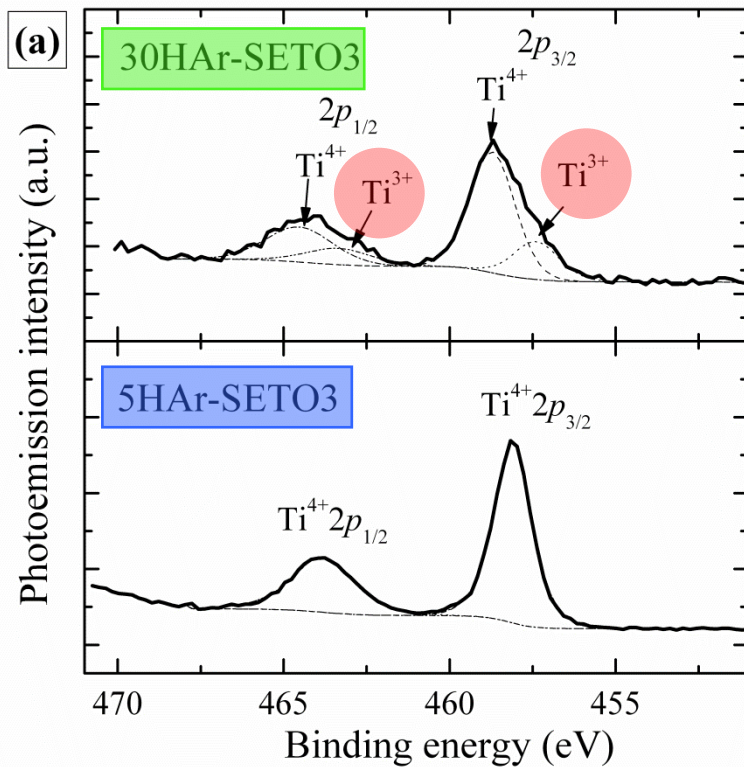
Ti 2p

$\text{Sr}_x\text{Eu}_{1-x}\text{TiO}_{3-\delta}$

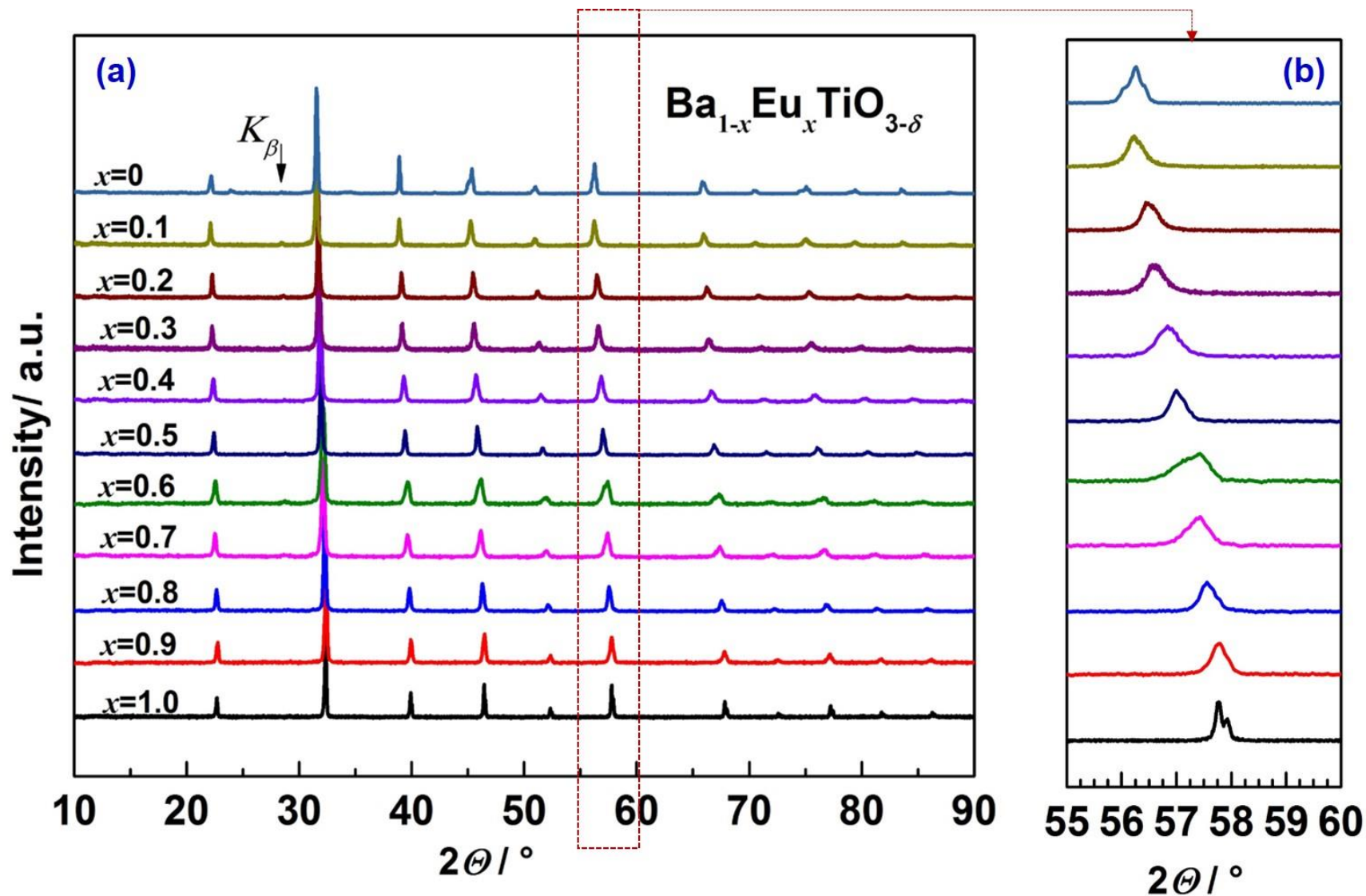
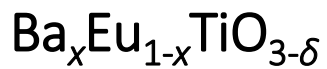
Eu 3d

30HAr: small
content of Ti^{3+}

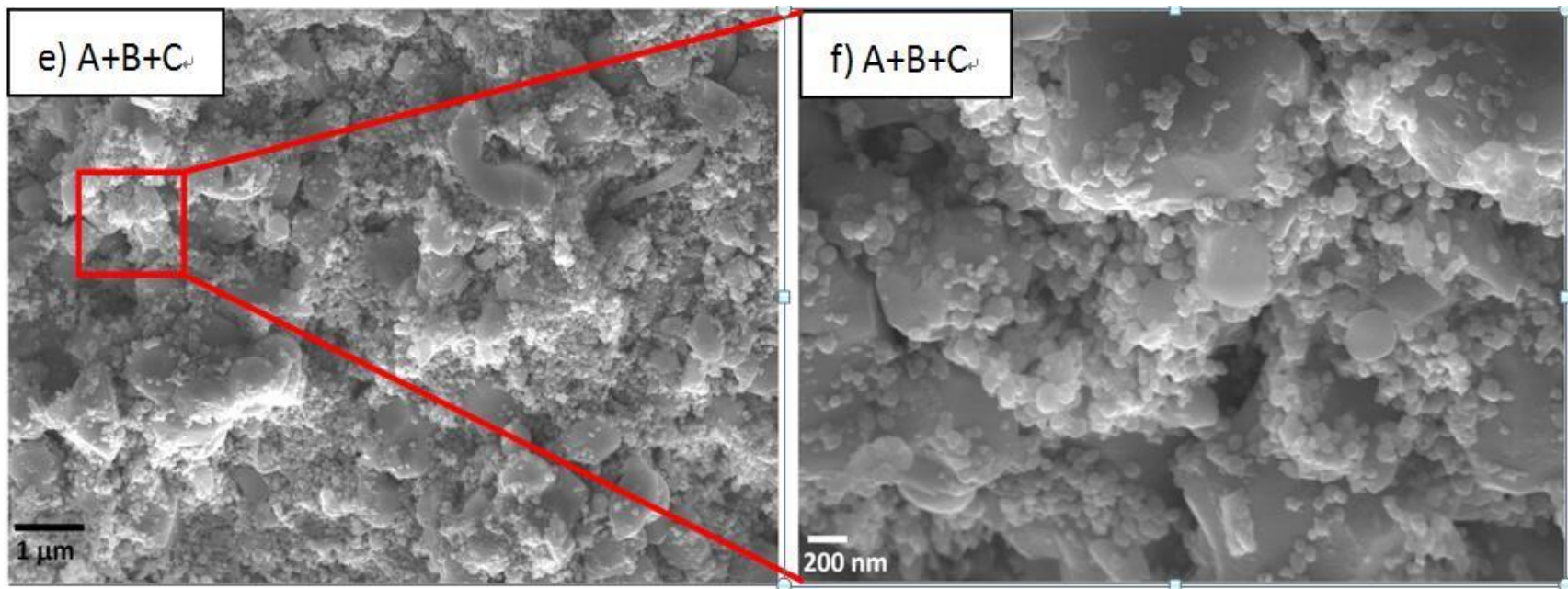
5HAr: larger content of
 Eu^{3+} than 30HAr



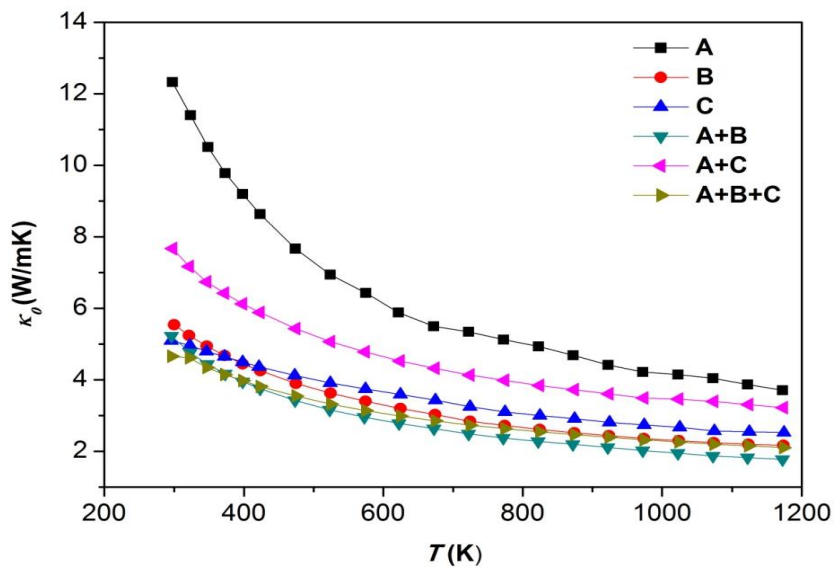
Ratio: $\text{Eu}^{3+}/\text{Eu}^{2+}$

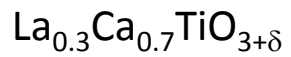
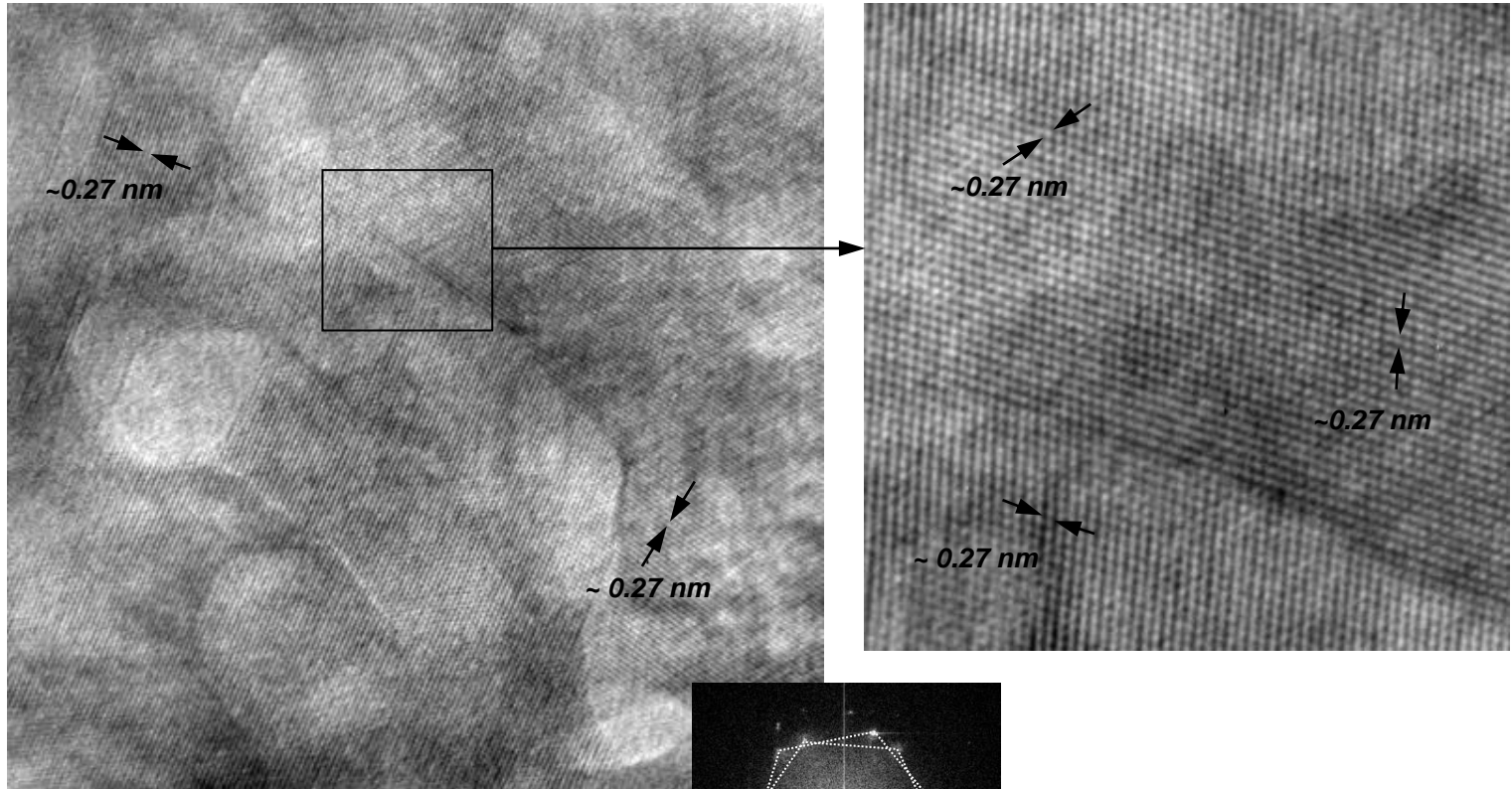


Multi-sized titanate particles

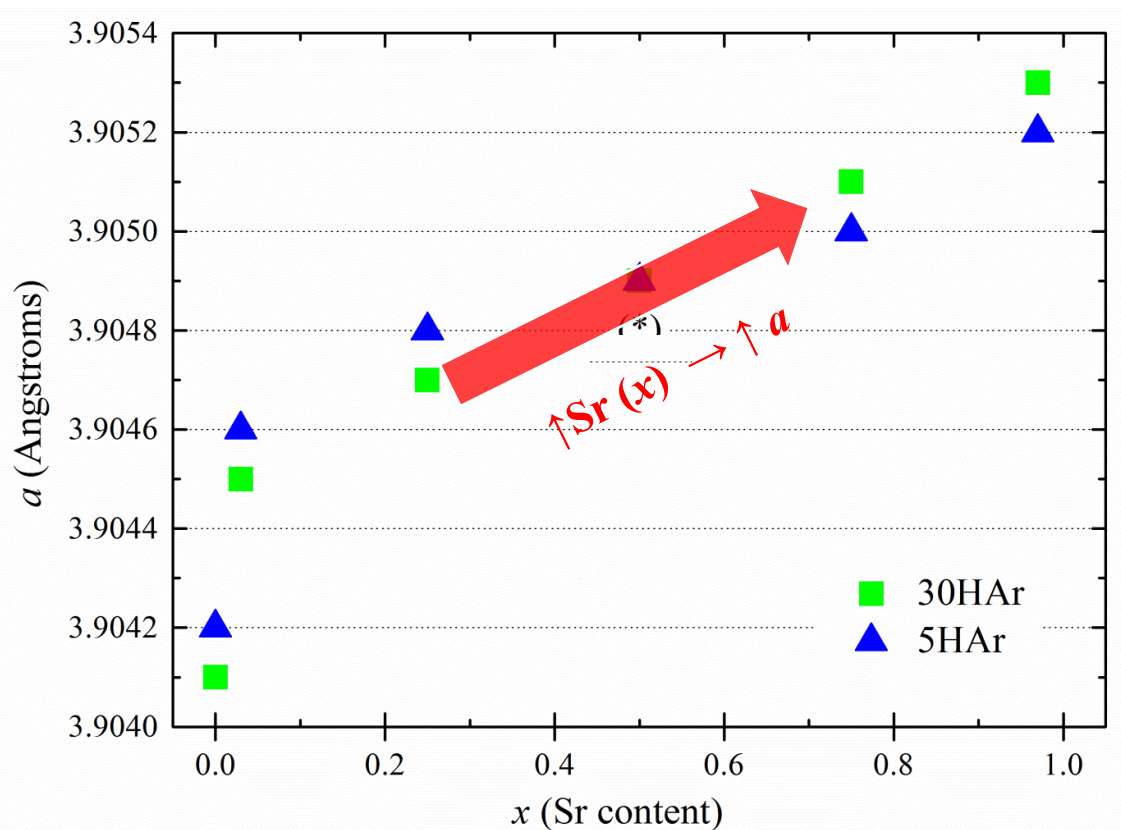
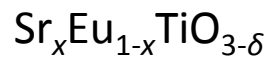


A+B+C 5 μm+500 nm
 +50 nm





Fast Fourier Transform of micrograph possesses mainly the overlapped diffraction patterns of a few grains with zone axis $[-111]$



$r(\text{Ti}^{3+}) > r(\text{Ti}^{4+})$

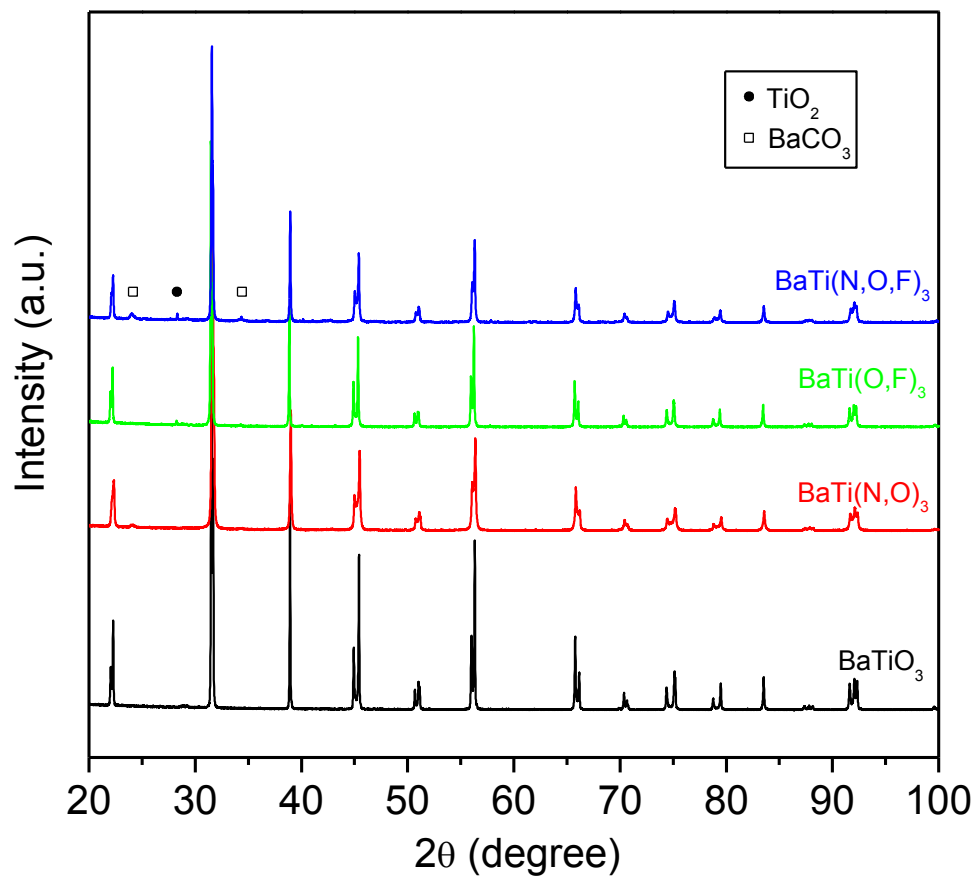
Phase pure XRD patterns: no traces of the pyrochlore $\text{Eu}_2\text{Ti}_2\text{O}_7$ phase

$\uparrow \text{Sr}(x) \rightarrow \uparrow a$

Sr^{2+} lower electronegativity than
slightly larger ionic radius than

Eu^{2+}

BaTi(O,N,F)

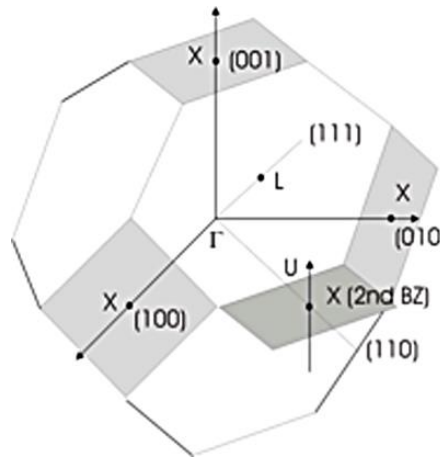


Mott equation for the Seebeck coefficient

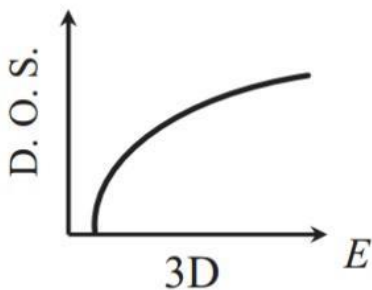
$$\alpha = \frac{\pi^2 k_B^2 T}{3e} \left\{ \frac{d[\ln(\sigma(E))]}{dE} \right\}_{E=E_F} = \frac{\pi^2 k_B}{3e} (k_B T) \left[\frac{1}{n(E)} \frac{dn(E)}{dE} + \frac{1}{\mu(E)} \frac{d\mu(E)}{dE} \right]$$

the Seebeck coefficient has two basic contributions: **the density of states (DOS) term** and **the scattering mechanism term** that intimately affects the mobility.

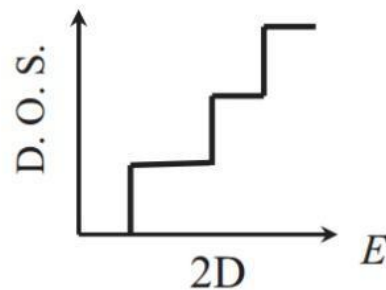
Brillouin zone



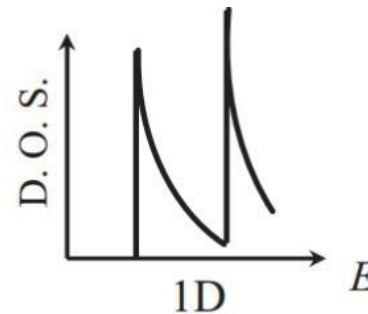
allowed states in k-space



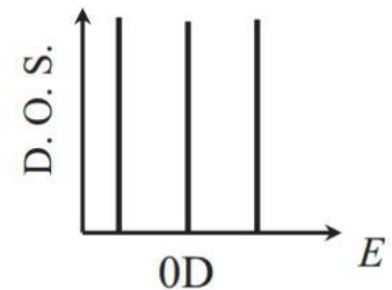
Bulk Semiconductor



Quantum Well



Quantum Wire



Quantum Dot

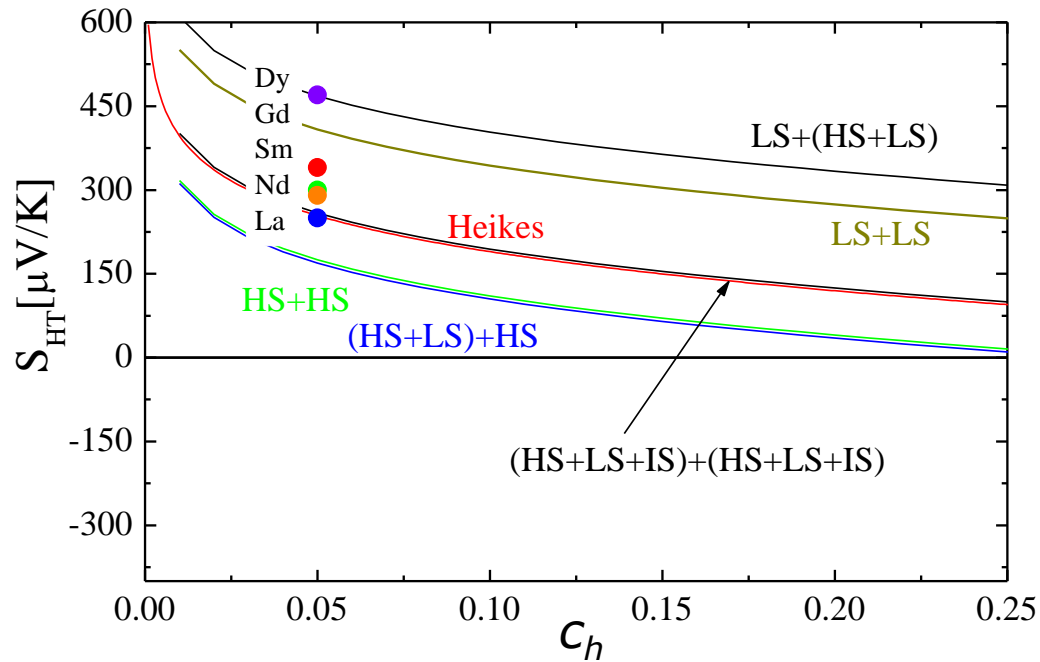
Seebeck coefficient of $\text{LnCo}_{0.95}\text{Ni}_{0.05}\text{O}_3$

Heikes:
$$S(T \rightarrow \infty) = + \frac{k_B}{|e|} \ln \left(\frac{1-x}{x} \right)$$

Spin-orbital entropy term

➤ + Spin & orbital degeneracy:
$$S(T \rightarrow \infty) = + \frac{k_B}{|e|} \ln \left(\frac{g_4}{g_3} \frac{1-c_h}{c_h} \right)$$

W. Koshibae, et al., PRB 62, 6869, 2000.



Design rules

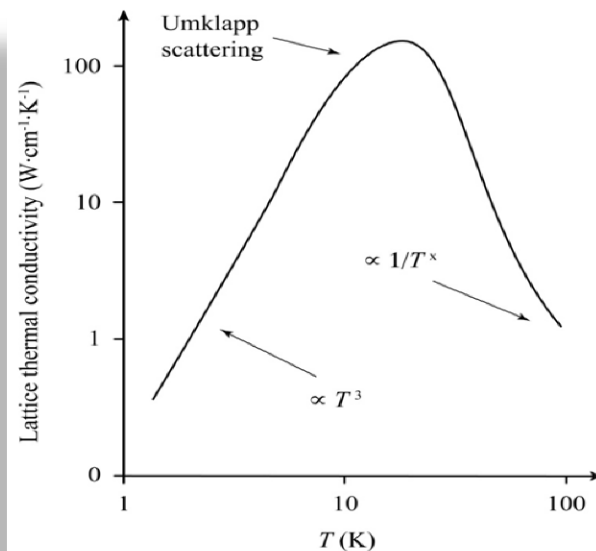
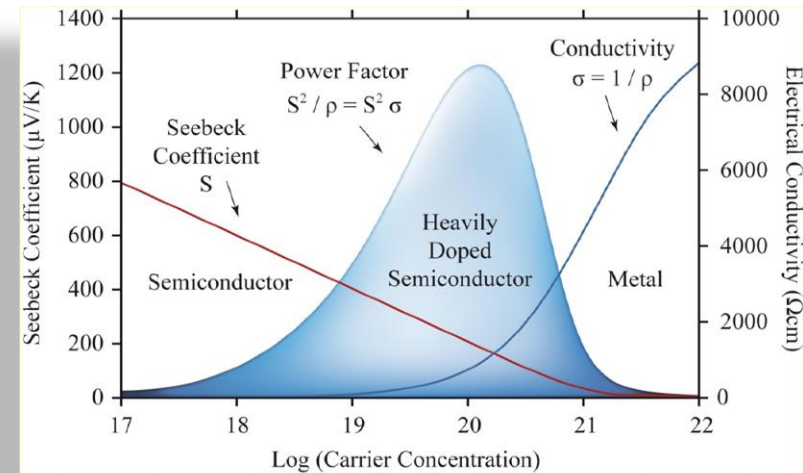
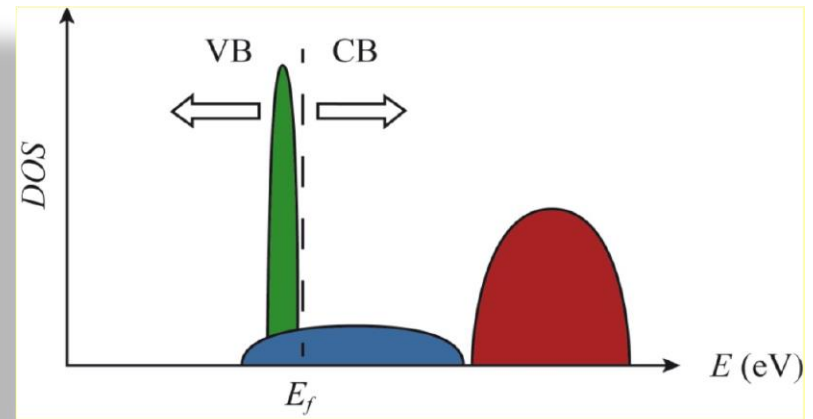
$$ZT = \frac{S^2 \sigma}{\kappa} T$$

S: Large dn/dE at $E = E_f$

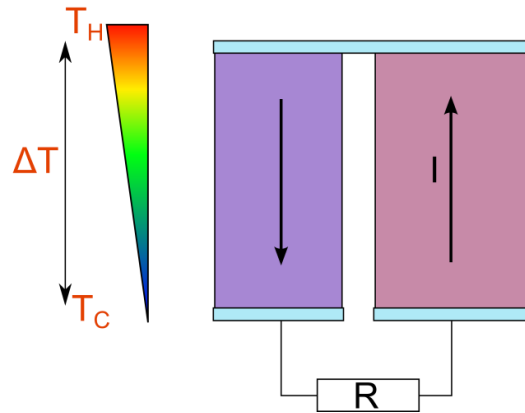
Large gap => Low Dimensional Systems, Large Effective Mass (m^*), Limit Minority Carriers, Spin entropy

σ : High charge carrier concentration and mobility
Narrow Gap, Low Electron Scattering, Correlated electrons

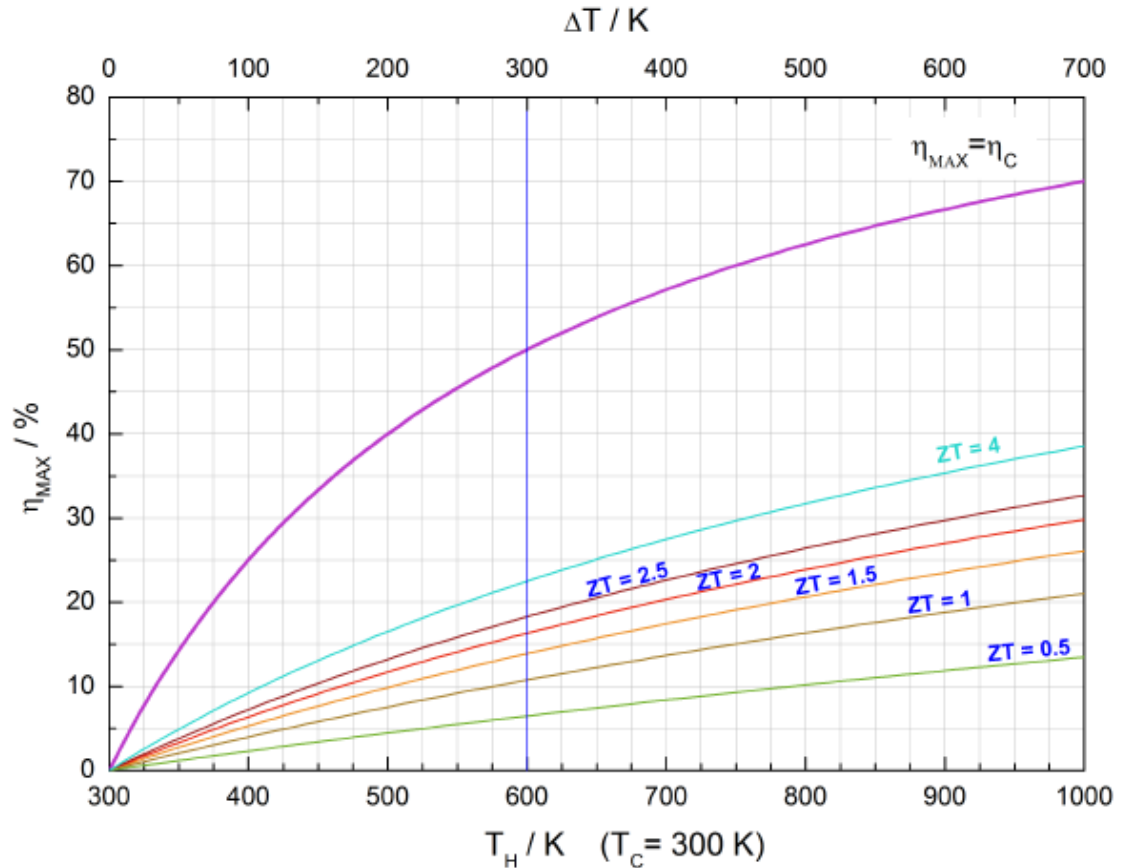
κ : Scatter Phonons, mass fluctuation, heavy atoms, Complex Structure, Defect & Grain Boundary



Thermocouple

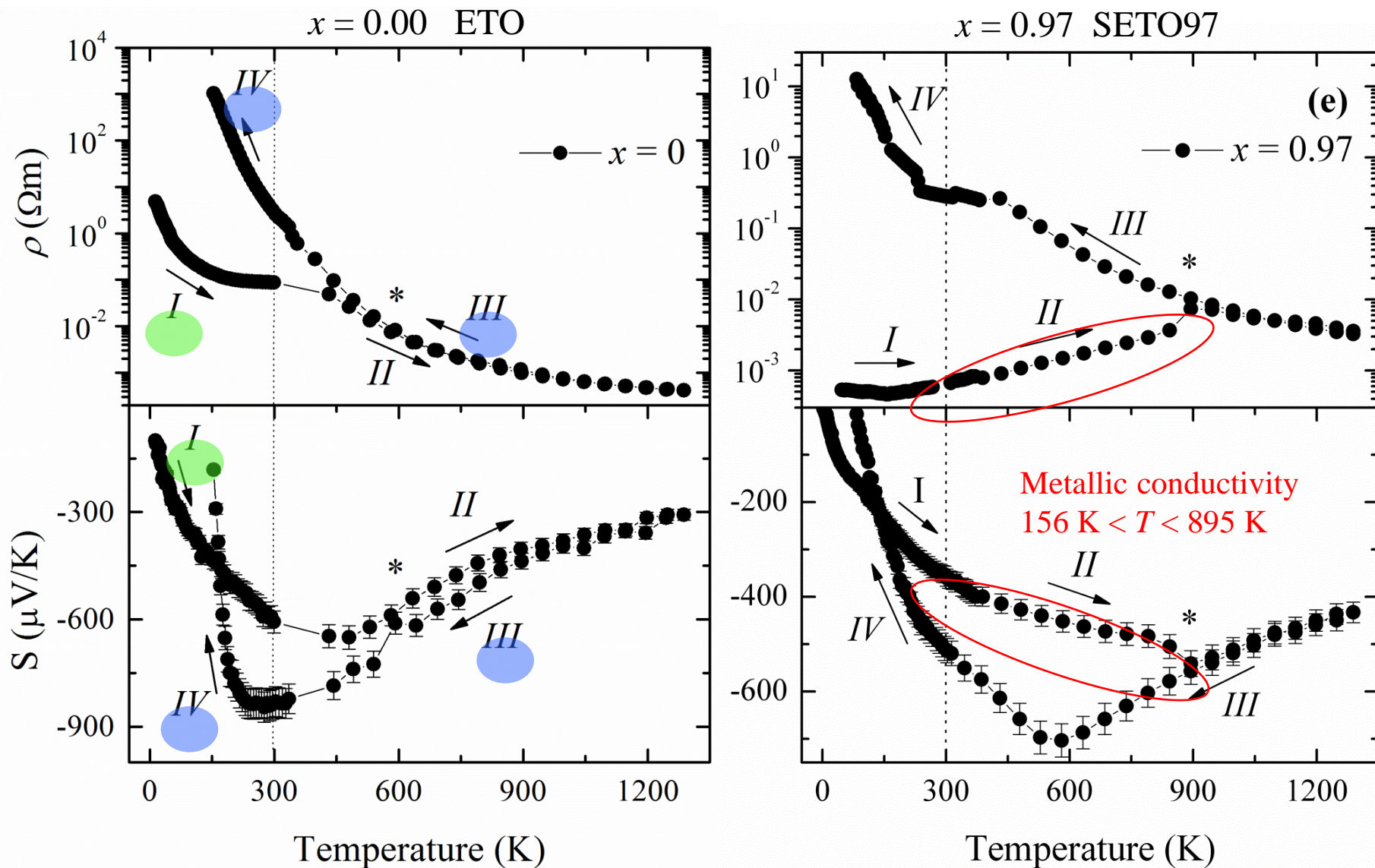


$$\eta_{max} = \eta_C \frac{\sqrt{1 + Z_{rel}\bar{T}} - 1}{\sqrt{1 + Z_{rel}\bar{T}} + \frac{T_C}{T_H}}$$

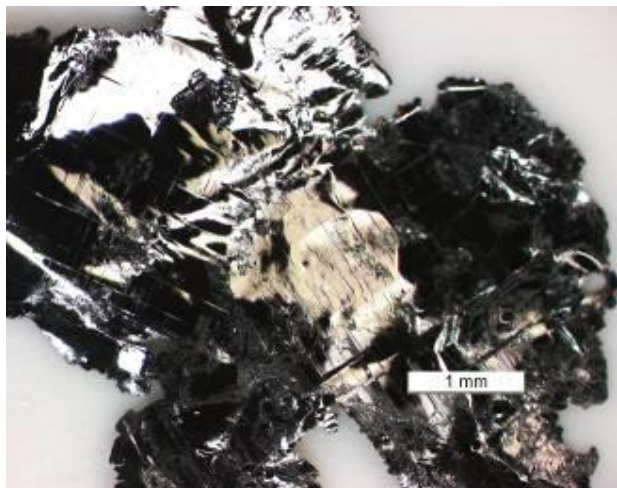


Conversion efficiency depends on the parameter $Z_{rel} = \frac{\alpha_{21}^2}{r_{12}k_{12}} = \frac{(\alpha_2 - \alpha_1)^2}{(r_1 + r_2)(k_1 + k_2)}$

Electrical resistivity and Seebeck coefficient

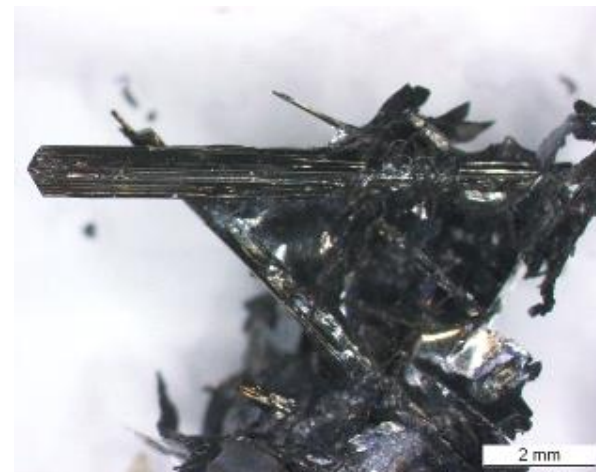


Uniaxial alignment and single crystal growth

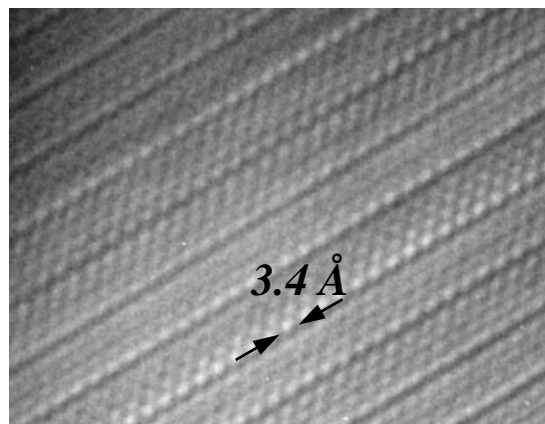
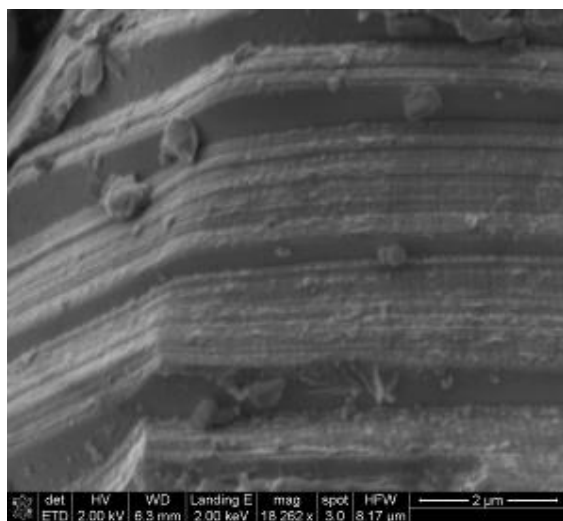


Aim:

High density
with
uniaxial alignment

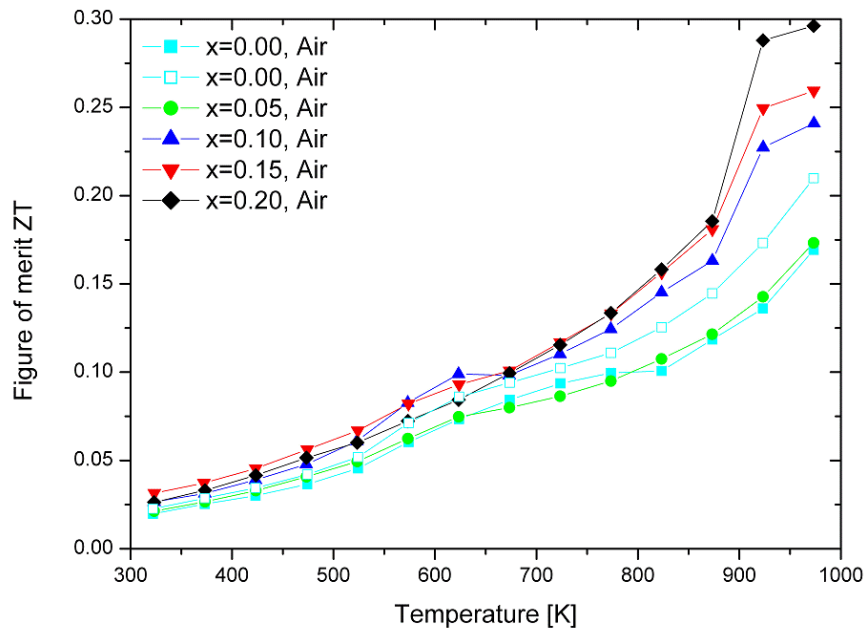
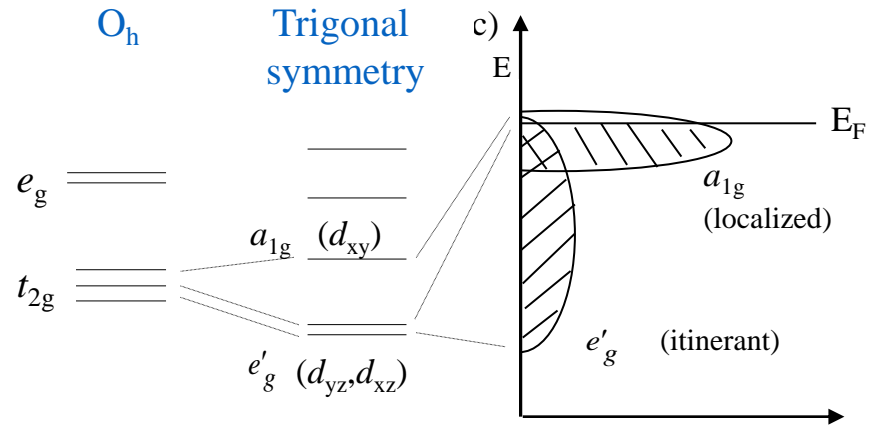
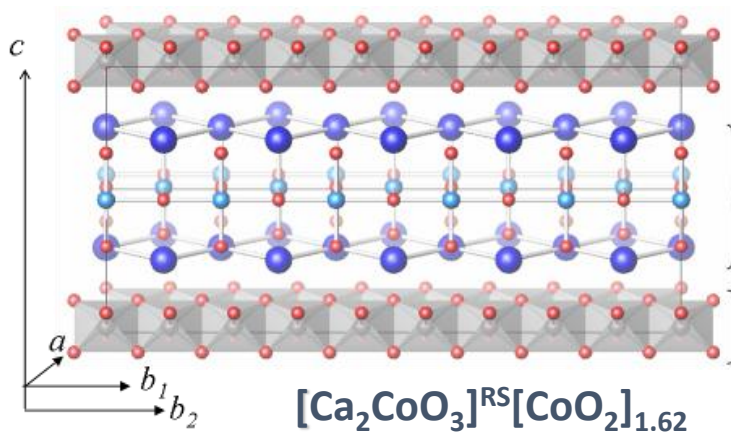


- recrystallization of Ca349 from potassium chloride/carbonate flux.

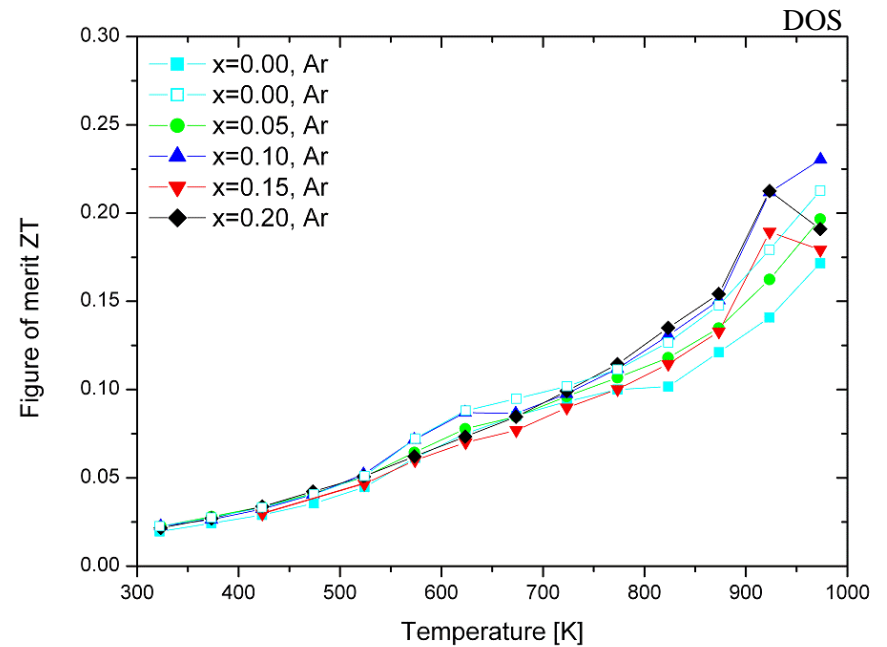


$$\begin{aligned} a &= 4.8 \text{ \AA}, \\ b_1 &= 4.5 \text{ \AA}, \\ c &= 10.8 \text{ \AA}, \\ b_2 &= 2.8 \text{ \AA} \\ \beta &\approx 98^\circ \\ \gamma &\approx 91^\circ \end{aligned}$$

ZT of p-type « $\text{Ca}_{3-x}\text{Bi}_x\text{Co}_4\text{O}_{9+\delta}$ ($0 < x < 0.2$)»



$0.3 < \delta < 0.5$



$0.0 < \delta < 0.3$

High temperature Solar Thermoelectric converters

Solar Power Concentrator

